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(54) **MICRO-LED TRANSFERRING METHOD AND MANUFACTURING METHOD OF MICRO-LED DEVICE**

MIKRO-LED-ÜBERTRAGUNGSVERFAHREN UND HERSTELLUNGSVERFAHREN EINER
MICRO-LED-VORRICHTUNG

PROCÉDÉ DE TRANSFERT DE MICRO-DELS ET PROCÉDÉ DE FABRICATION D'UN DISPOSITIF
À MICRO-DELS

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Description

FIELD OF THE INVENTION

[0001] The present disclosure relates to Micro-Light Emitting Diode (micro-LED) array for display. The claimed invention relates to a method for transferring micro-LED, a method for manufacturing a micro-LED device. Also disclosed are a micro-LED device and an electronic apparatus containing a micro-LED device.

BACKGROUND OF THE INVENTION

[0002] The micro-LED technology refers to the LED array of small size integrated on a substrate with high density. Currently, the micro-LED technology is starting development, and it is expected in the industry that a high-quality micro-LED product comes into the market. High-quality micro-LED will have a deep affection on the conventional display products such as LCD/OLED that have already been put into the market.

[0003] In the process of manufacturing micro-LEDs, micro-LEDs are first formed on a donor wafer, and then the micro-LEDs are transferred to a receiving substrate. The receiving substrate is a display screen, for example.

[0004] One difficulty during manufacturing a micro-LED lies in how to transfer a micro-LED from a donor wafer to a receiving substrate. In the prior art, the transfer is generally performed by means of electrostatic pick-up. A transfer head array will be needed during the electrostatic pick-up. The structure of the transfer head array is relatively complicated, and the stability thereof shall be considered. An extra cost shall be paid for manufacturing a transfer head array. A phase change shall be made before pick-up with the transfer head array. In addition, during manufacturing with a transfer head array, limitations apply to the thermo budget of a micro-LED for phase change, which is generally lower than 350°C, or more specifically, lower than 200°C; otherwise, the performance of the micro-LED will be degraded. It generally requires two transfers during the manufacturing with transfer head array, i.e., the transfer from a donor wafer to a carrier wafer and the transfer from the carrier wafer to a receiving substrate.

[0005] US patent No. 8,333,860B1 discloses an array of transfer heads for transferring micro devices, in which a voltage is applied to the electrode in the transfer head to pick-up a micro device.

[0006] US patent No. 8,426,227B1 discloses a method of forming a micro light emitting diode array, in which a micro-LED array is transferred to a receiving substrate by using a transfer head array.

[0007] US 2011/0151602 A1 relates to the manufacture of transferable elements including LEDs and other devices. There is used an optical system, which may be a mesh, a grid, a template, or a lens array which form a separate system, but no layer formed on the original substrate.

[0008] US 2011/0133216 A1 discloses a method of manufacturing semiconductor light-emitting devices and stacked structure bodies.

[0009] WO 2015/107290 A2 discloses a process for placing and bonding chips on a receiver substrate wherein an electromagnetic force could be applied to a chip through pads.

SUMMARY OF THE INVENTION

[0010] One object of this invention is to provide a new technical solution for transferring micro-LEDs. This object is achieved by the combination of the features of claim 1. There is provided a method for transferring micro-LEDs, comprising: forming a mask layer on the back-side of a laser-transparent original substrate, wherein micro-LEDs are formed on the front-side of the original substrate; bringing the micro-LEDs on the original substrate in contact with preset pads on a receiving substrate; and irradiating the original substrate from the original substrate side with laser through the mask layer, to lift-off micro-LEDs from the original substrate, wherein during the micro-LEDs is lifted-off from the original substrate, a contactless action is applied onto the micro-LEDs, and the contactless action is electromagnetic force.

[0011] Preferably, the original substrate is a sapphire substrate, and the thickness range of the original substrate is 20-1000 μ m, or 50-500 μ m, or 100-300 μ m.

[0012] Preferably, the spatial resolution range of the mask layer is 1-50 μ m.

[0013] Preferably, the material of the mask layer is selected from photoresist, polymer, metal/metal compound, metal/metal alloy, metal/metal composite, silicon and silicide.

[0014] Preferably, the micro-LEDs are in contact with the pad through micro-bump bonding.

[0015] Preferably, the laser beam size of the laser is 50-5000 μ m.

[0016] Preferably, the micro-LEDs are arranged on the receiving substrate in a redundant manner.

[0017] According to another embodiment of the present invention, there is provided a method for manufacturing a micro-LED device, comprising transferring micro-LEDs onto a receiving substrate of the micro-LED device by using the method according to the present invention.

[0018] According to another embodiment not forming part of the claimed invention, there is provided a micro-LED device, which is manufactured by using the method according to the present invention.

[0019] According to another embodiment not forming part of the claimed invention, there is provided an electronic apparatus, containing a micro-LED device. It should be understood by a person skilled in the art that content which is not mentioned in a claim should not be regarded as a limitation to said claim.

[0020] Further features of the present invention and advantages thereof will become apparent from the fol-

lowing detailed description of exemplary embodiments, some of which are embodiments of the claimed invention, with reference to the attached drawings. The invention is as defined in the appended claims.

BRIEF DISCRIPTION OF THE DRAWINGS

[0021] The accompanying drawings, which are incorporated in and constitute a part of the specification, illustrate embodiments, some of which are embodiments of the invention and, together with the description thereof, serve to explain the principles of the invention.

Figure 1 shows a flow chart of an illustrative embodiment of the method according to the present disclosure.

Figure 2A to 2G shows an example for transferring a micro-LED according to the present disclosure.

Figure 3 shows a flow chart of another illustrative embodiment of the method according to the present disclosure.

Figures 4A to 4L show another example for transferring a micro-LED according to the present disclosure.

Figure 5 shows a flow chart of still another illustrative embodiment of the method according to the present disclosure.

Figures 6A to 6F show an example for transferring red micro-LEDs according to the present disclosure. Figures 7A to 7L show still another example for transferring a micro-LED according to the present disclosure.

Figure 8 shows still an example for transferring a lateral micro-LED according to the present disclosure.

Figure 9 shows still another example for transferring a lateral micro-LED according to the present disclosure.

Figure 10 shows a flow chart of still another illustrative embodiment of the method according to the present disclosure.

Figure 11 shows a flow chart of still another illustrative embodiment of the method according to the present disclosure.

Figures 12A to 12F show an example for repairing micro-LED defects according to the present disclosure.

Figure 13 shows a flow chart of still another illustrative embodiment of the method according to the present disclosure.

Figures 14A to 14C show an example for pre-screening defect micro-LEDs according to the present disclosure.

Figures 15A to 15B show another example for pre-screening defect micro-LEDs according to the present disclosure.

Figures 16A to 16B is an enlarged view of the area "A" of Figure 15B.

Figure 17 shows a flow chart of still another illustrative embodiment of the method according to the present disclosure.

Figures 18A to 18J show an example for transferring micro-LEDs at wafer level according to the present disclosure.

Figure 19 shows a flow chart of still another illustrative embodiment of the method according to the present invention.

Figures 20A to 20I show another example for transferring micro-LEDs according to the present invention.

DETAILED DESCRIPTION OF THE EMBODIMENTS

[0022] Various exemplary embodiments, some of which are embodiments of the claimed invention will now be described in detail with reference to the drawings. It should be noted that the relative arrangement of the components and steps, the numerical expressions, and numerical values set forth in these embodiments do not limit the scope of the present invention unless it is specifically stated otherwise.

[0023] The following description of at least one exemplary embodiment is merely illustrative in nature and is in no way intended to limit the invention, its application, or uses.

[0024] Techniques, methods and apparatus as known by one of ordinary skill in the relevant art may not be discussed in detail but are intended to be part of the specification where appropriate.

[0025] In all of the examples illustrated and discussed herein, any specific values should be interpreted to be illustrative only and non-limiting. Thus, other examples of the exemplary embodiments could have different values.

[0026] Notice that similar reference numerals and letters refer to similar items in the following figures, and thus once an item is defined in one figure, it is possible that it need not be further discussed for following figures.

[0027] Embodiments and examples of the present disclosure, some of which are embodiments of the claimed invention, will be described below with reference to the drawings.

[0028] Fig. 1 shows a flow chart of an illustrative embodiment of the method for transfer micro-LED according to the present disclosure.

[0029] As shown in Fig. 1, at step S1100, a micro-LED is formed on a laser-transparent original substrate.

[0030] The laser-transparent original substrate can be a sapphire substrate, SiC substrate and so on, for example. The micro-LED can be used for being mounted on a display screen panel.

[0031] It should be understood by a person skilled in the art that one micro-LED could be formed on the original substrate, or a plurality of micro-LED could be formed on the original substrate. For example, a plurality of micro-LEDs can be formed on the laser-transparent original

substrate. The plurality of micro-LEDs can form an array.

[0032] In an example, in a case where a plurality of micro-LEDs are formed on the laser-transparent original substrate, the original substrate can be singulated or divided into multiple pieces for more flexible transferring.

[0033] At step S1200, the micro-LED is brought into contact with a pad preset on a receiving substrate.

[0034] For example, the receiving substrate is a display screen panel.

[0035] For example, the pad can be set for red pixel array, yellow pixel array or blue pixel array.

[0036] In an example, in a case where a plurality of micro-LED are formed, at least one micro-LED of the plurality of micro-LEDs can be brought into contact with at least one pad preset on the receiving substrate. The at least one micro-LED could be one, several or all of the plurality of micro-LEDs. It should be understood by a person skilled in the art that, although it is just described here that at least one micro-LED, which is expected to be lifted-off, is in contact with a pad, a remaining micro-LED of the plurality of micro-LEDs can also be in contact with a pad.

[0037] For example, in the step of contact (S1200), the micro-LED can be brought into contact with the pad preset on the receiving substrate via a liquid thin film. For example, the liquid thin film can include flux. Herein, the lift-off of a micro-LED will be easy through the surface tension force of the liquid thin film (flux), and the successful rate is high.

[0038] At step S1300, the original substrate is irradiated with laser from the original substrate side to lift-off the micro-LED from the original substrate.

[0039] In an example, in a case where at least one micro-LED is in contact with pad, at least one area on the original substrate can be irradiated with laser from the original substrate side to lift-off the at least one micro-LED from the original substrate. For example, a technician can select the at least one area. For example, the at least one area corresponds to the at least micro-LED, respectively. The at least one area can be just partial area on the original substrate, or can be the whole area.

[0040] In another example, the original substrate can be offset for transferring additional micro-LEDs.

[0041] In another example, after the transferring using the original substrate, an additional laser-transparent backup substrate can be used to cope with a situation in which micro-LEDs are missing at some points on the display screen panel. For example, a micro-LED can be formed on an additional laser-transparent backup substrate; the micro-LED on the backup substrate is brought into contact with a pad preset on a receiving substrate; and the backup substrate is irradiated with laser from the backup substrate side to lift-off the micro-LED from the backup substrate. In such a way, the quality of a display screen can further be improved.

[0042] An array of micro-LEDs can be formed on the receiving substrate after the transferring of micro-LEDs to the receiving substrate.

[0043] After the transferring of micro-LEDs to the receiving substrate, the present disclosure can further include subsequent steps.

[0044] For example, the lifted-off micro-LEDs can be reflow-soldered on the receiving substrate. A negative electrode can be deposited on the micro-LEDs. The reflow-soldering can be performed after micro-LEDs of each color are transferred. Alternatively, the reflow-soldering can be performed after micro-LEDs of all colors are transferred.

[0045] In addition, the soldered micro-LED can be filled with polymer. For example, a confocal dielectric deposition can be used in stead of polymer filling.

[0046] In another embodiment, the present disclosure further includes a method for manufacturing a micro-LED device. The manufacturing method comprises transferring a micro-LED to a receiving substrate by using the method for transferring a micro-LED according to the present disclosure.

[0047] In another embodiment, the present disclosure further includes a micro-LED device, such as a display screen device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device according to the present disclosure.

[0048] In comparison with the prior art, under the similar conditions, the micro-LED manufactured by using the solution of the present disclosure is relatively simple and reliable while maintaining a high quality, and the throughput thereof is relatively high with low cost.

[0049] In another embodiment, the present disclosure further includes an electronic apparatus. The electronic apparatus contains a micro-LED device according to the present invention. For example, the electronic apparatus can be a mobile phone, a pad computer and so on.

[0050] In the solution of the present disclosure, a micro-LED is formed directly on the original substrate and it is transferred to a receiving substrate by means of laser lift-off.

[0051] In addition, the micro-LED can be selectively transferred through the present disclosure.

[0052] In addition, in the solution of the present disclosure, the transfer can be performed only once while two transfers are needed in the prior art.

[0053] In addition, in comparison with the prior art, the solution of the present disclosure is relatively efficient, the cost is relatively low and product performance degrade due to an extra thermal budget will not occur.

[0054] In addition, in comparison with the prior art using a pick-up head, the present disclosure does not need a complicated pick-up system, and thus the cost of product manufactured using the present disclosure will be relatively low and reliable.

[0055] In addition, since it does not need the temporary bonding in the prior art between the micro-LED and the intermediate carrier substrate, the cost can be further decreased by this disclosure.

[0056] Since it is not necessary to consider the phase change of bonding layer considered in the prior art using

pick-up head, the manufacturing method of the present disclosure can have a relatively high through put and the extra thermal load limitation will be less. Consequently, under the similar conditions, the manufactured micro-LED will have a higher performance.

[0057] An example for transferring a micro-LED according to the present disclosure will be described below with reference to Figs. 2A to 2G.

[0058] As shown in Fig. 2A, micro-LEDs 2 are formed on a laser-transparent original substrate 1 such as sapphire substrate. The micro-LEDs 2 have a vertical micro-LED structure, for example. The micro-LEDs 2 contains, for example, a n-doped GaN layer, a multiple quantum well structure, a p-doped GaN layer, a p metal electrode, a bump, and so on.

[0059] As shown in Fig. 2A, the plurality of micro-LEDs 2 can be singulated.

[0060] As shown in Fig. 2B, the original substrate 1 is flipped over, and is aligned with a receiving substrate 4 with liquid thin film (for example, containing flux) 5. The micro bumps on the micro-LEDs are in contact with the flux. Pads 3 are preset on the receiving substrate 4. For example, the pads 3 include pad 3r for receiving red micro-LED, pad 3b for receiving blue micro-LED and pad 3g for receiving green micro-LED.

[0061] As shown in Fig. 2C, partial areas 7 on the original substrate are selectively irradiated with laser 7, to lift off the selected micro-LEDs 2a, 2b of the plurality of formed micro-LEDs from the original substrate.

[0062] As shown in Fig. 2D, the original substrate 1 is lifted up. Because of the function of the surface tension force of the liquid thin film, the selected micro-LEDs 2a, 2b are lifted-off easily, while the other micro-LEDs are remained on the original substrate 1.

[0063] Then, the original substrate is moved and the operations of Figs. 2C to 2D are repeated, so that a plurality of micro-LEDs are transferred to the receiving substrate.

[0064] As shown in Fig. 2E, the plurality of micro-LEDs are transferred to the receiving substrate 4.

[0065] As shown in Fig. 2F, for example, the plurality of micro-LEDs are soldered onto the receiving substrate through reflow soldering. Then, the flux is cleaned.

[0066] As shown in Fig. 2G, the receiving substrate is filled with polymer 8 and is sealed. Then, n-metal electrode 9 is deposited, for example, using ITO material.

[0067] Figure 3 shows a flow chart of another illustrative embodiment of the method for transferring a micro-LED according to the present disclosure.

[0068] As shown in Figure 3, at step S2100, micro-LEDs are formed on a laser-transparent original substrate.

[0069] At step S2200, an anisotropic conductive layer is provided on a receiving substrate.

[0070] For example, the anisotropic conductive layer is at least one of an anisotropic conductive film (ACF), an anisotropic conductive paste (ACP) and an anisotropic conductive tape (ACT).

[0071] At step S2300, the micro-LEDs are brought into contact with the anisotropic conductive layer on the receiving substrate. For example, the micro-LEDs are adhered to the anisotropic conductive layer on the receiving substrate. At this step, the micro-LEDs can be aligned with the receiving substrate in advance, for example.

[0072] At step S2400, the original substrate is irradiated with laser from the original substrate side to lift-off the micro-LEDs from the original substrate.

[0073] For example, the above steps can be performed with respect to red micro-LEDs, green micro-LEDs and blue micro-LEDs, respectively. Since the transfer with respect to the three micro-LEDs can be regarded as a simple repeat of the above steps, they are not repeated here. As long as each of the above steps are performed in a solution, the solution will be covered by this disclosure.

[0074] At step S2500, the anisotropic conductive layer is processed to electrically connect the micro-LEDs (its electrodes) with the pads on the receiving substrate.

[0075] In an example, pressure can be applied on the anisotropic conductive layer from the micro-LED side by using an auxiliary substrate. For example, the temperature of processing the anisotropic conductive layer can be between 150°C and 200°C. For example, the applied pressure is between 1 MPa and 4 MPa. For example, the time period of applying pressure is between 10 second and 30 second.

[0076] In an example, the auxiliary substrate can be a flat rigid substrate. The inventors of the present application have found that the possible displacement of the micro-LEDs can be reduced by using a rigid substrate. This point has not noticed by a person skilled in the art.

[0077] For example, the surface of the auxiliary substrate can be coated with temporary bonding polymer. In this situation, the step S2500 can further comprises: bonding the auxiliary substrate with the anisotropic conductive layer via the temporary bonding polymer; and after applying pressure, de-bonding the auxiliary substrate via the temporary bonding polymer, to remove the auxiliary substrate. The advantage of temporarily bonding the auxiliary substrate with the anisotropic conductive layer lies in that, the positions of the micro-LEDs can be relatively fixed, and the displacement of micro-LEDs during processing the anisotropic conductive layer is reduced.

[0078] After the above processes, normal subsequent processes can be done on the micro-LEDs. For example, the subsequent processes include: etching the temporary bonding polymer, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes on the epitaxial layers of the micro-LEDs; and performing encapsulation on the N-metal electrodes.

[0079] For example, the receiving substrate can be a display substrate. Leads and pads can be set on the receiving substrate in advance, to be electronically connect with the micro-LEDs.

[0080] In this embodiment, the micro-LEDs and the re-

ceiving substrate are connected through a anisotropic conductive layer. This approach of processing is relatively simple and is more suitable for production in large bulk.

[0081] In another embodiment, the present disclosure further provides a method for manufacturing a micro-LED device. The manufacturing method comprises transferring micro-LEDs to a receiving substrate by using the method according to the present disclosure. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0082] In another embodiment, the present disclosure further provides a micro-LED device, such as a display device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device according to the present disclosure. In the micro-LED device according to the embodiment, the micro-LEDs come into electronic contact with the pads on the receiving substrate via the anisotropic conductive layer, which is different from the micro-LED device in the prior art.

[0083] In another embodiment, the present disclosure further provides an electronic apparatus. The electronic apparatus contains a micro-LED device according to the embodiment. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0084] Figure 4A to 4L shows another example for transferring a micro-LED according to the present disclosure.

[0085] As shown in Figure 4A, an original substrate 201 such as a sapphire substrate has red micro-LEDs 202 thereon. The receiving substrate 204 such as display substrate has an anisotropic conductive film (ACF) 203 thereon. The receiving substrate 204 has signal leads 205 and pads 205' for connecting micro-LEDs.

[0086] As shown in Figure 4B, the original substrate 201 (red micro-LED 202) is brought into contact with the anisotropic conductive film 203 with a light force. For example, the red micro-LEDs 202 to be transferred can be aligned with the pads on the receiving substrate 204. The original substrate 201 is irradiated with laser 206, to selectively lift-off red micro-LEDs.

[0087] Figure 4C shows lifted-off red micro-LEDs 202r.

[0088] Figure 4D shows an original substrate 207 and the green micro-LEDs 208 thereof. The green micro-LEDs to be lifted-off are aligned with the pads on the receiving substrate 204.

[0089] Figure 4E shows the situation in which the green micro-LEDs 208 are in contact with the anisotropic conductive film 203 with a light force. At least one green micro-LED is selectively lifted-off by using laser 209.

[0090] Figure 4F shows lifted-off red micro-LEDs 202r and green micro-LEDs 208g.

[0091] Figure 4G shows an original substrate 210 and the blue micro-LEDs 211 thereof. The blue micro-LEDs to be lifted-off are aligned with the pads on the receiving substrate 204.

[0092] Figure 4H shows the situation in which the blue micro-LEDs 211 are in contact with the anisotropic con-

ductive film 203 with a light force. At least one blue micro-LED is selectively lifted-off by using laser 212.

[0093] Figure 4F shows lifted-off red micro-LEDs 202r, green micro-LEDs 208g and blue micro-LEDs 211b.

[0094] After the transfer of micro-LEDs in the three colors, an inspection and repair can be performed with respect to any defect.

[0095] Figure 4J shows an auxiliary substrate 213. The auxiliary substrate 213 is a flat rigid substrate, such a glass substrate. Polymer 214 such as 3M LC5200/5320 is coated on the auxiliary substrate 213. The polymer can be cured through UV and can be de-bonded through red laser.

[0096] In Figure 4K, the ACF 203 is processed through the auxiliary substrate 213. For example, the processing condition is that the temperature is between 150°C and 200°C, the applied pressure is between 1 MPa and 4 MPa, the time period of applying pressure is between 10 second and 30 second. Through these processes, the ACF 203 interconnects the micro-LEDs with corresponding pad in the vertical direction.

[0097] Then, the auxiliary substrate 213 is de-bonded (through the polymer 214).

[0098] In Figure 4L, the normal subsequent processes are performed: etching the polymer 214, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes 215 (for example, ITO electrodes) on the epitaxial layers of the micro-LEDs; and performing encapsulation 216 on the N-metal electrodes (for example, PET lamination).

[0099] Figure 5 shows a flow chart of still another illustrative embodiment of the method for transferring a micro-LED according to the present disclosure.

[0100] As shown in Figure 5, at step S3100, at least one micro-LED is transferred from an original substrate to a support body. For example, the original substrate is laser-transparent.

[0101] In an example, this step can comprises: mounting the original substrate onto the support body, wherein the micro-LEDs are formed on the original substrate, the support body has light-release adhesive on its surface, and the micro-LEDs are adhered to the support body via the light-release adhesive; irradiating the original substrate with laser from the original substrate side, for lifting-off the at least one micro-LED from the original substrate, and irradiating light from the support body side, to release un-lifted-off micro-LEDs. In this example, the support body is transparent.

[0102] For example, the light-release adhesive can be a UV tape. For example, the support body is stiff. The displacement of micro-LEDs during transfer will have affect on the quality of the final product. The inventors of this application have found that this displacement can be reduced by using a stiff support body. This point has not been noticed by a person skilled in the art. For example, the material of the support body can be PET.

[0103] Generally, it is difficult to form red micro-LEDs on a laser-transparent substrate such as a sapphire sub-

strate. Accordingly, in an example, the red micro-LEDs are formed in advance and then are transferred to an original substrate, for being finally transferred to a receiving substrate. For example, in this embodiment, red micro-LEDs can be formed on a growth substrate. Then, the red micro-LEDs are transferred to an intermediate substrate. After that, the red micro-LEDs are transferred from the intermediate substrate to the original substrate.

[0104] At step S3200, the at least one micro-LED are transferred from the support body to a backup substrate.

[0105] For example, the backup substrate has elastomer or polymer on its surface. For example, the at least one micro-LED are bonded to the backup substrate through the elastomer or polymer.

[0106] In an example, this step can further comprises: bonding the support body with the at least one micro-LED to the backup substrate, and irradiating light from the support body side, to release the at least one micro-LED.

[0107] At step S3300, the at least one micro-LED are transferred from the backup substrate to a receiving substrate.

[0108] In an example, the step can further comprise: aligning the at least one micro-LED with the pads on the receiving substrate; and lifting-off the at least one micro-LED via the elastomer or polymer.

[0109] For example, the above transfer steps can be performed with respect to red micro-LEDs, blue micro-LEDs and green micro-LEDs, respectively. They will not be repeatedly described here.

[0110] After the above processes, normal subsequent processes can be done on the micro-LEDs. For example, the subsequent processes include: coating polymer on the receiving substrate with micro-LEDs; curing the polymer; etching the polymer, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes on the epitaxial layers of the micro-LEDs; and performing encapsulation on the N-metal electrodes.

[0111] The inventors have found that during the transfer of micro-LEDs, usually, only part of the micro-LEDs on the original substrate are transferred. If the micro-LEDs are directly transferred to a receiving substrate, the remaining micro-LEDs on the original substrate are often contaminated. In this embodiment, this contamination can be reduced through the transfer via an intermediate support body.

[0112] In another embodiment, the present disclosure further provides a method for manufacturing a micro-LED device. The manufacturing method comprises transferring micro-LEDs to a receiving substrate by using the method for transferring micro-LEDs according to this embodiment. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0113] In another embodiment, the present disclosure further provides a micro-LED device, such as a display device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device

according to said embodiment.

[0114] In another embodiment, the present disclosure further provides an electronic apparatus. The electronic apparatus contains a micro-LED device according to the embodiment. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0115] Generally, red micro-LEDs cannot be directly formed on a laser-transparent original substrate such as sapphire substrate. Thus, it is required that red micro-LEDs are formed on an additional substrate in advance, and then are transferred to a sapphire substrate. Figure 6A to 6F shows an example for transferring red micro-LEDs according to the present disclosure.

[0116] As shown in Figure 6A, red micro-LEDs 302 are formed on a growth substrate 301 such as GaAs substrate.

[0117] As shown in Figure 6B, the red micro-LEDs 302 are bonded with intermediate substrate 304 such as silicon substrate, through temporary bonding polymer 303. The polymer 303 is a thermal release tape (TRT), for example.

[0118] As shown in Figure 6C, the growth substrate 301 is removed by a wet etching method, for example.

[0119] As shown in Figure 6D, a light resist 305 is coated on an original substrate 306 such as sapphire substrate. The original substrate 306 and the red micro-LEDs 302 are bonded through the resist 305. The resist 305 can endure the temperature above 200°C; generally above 250°C.

[0120] As shown in Figure 6E, the polymer 303 is processed under a temperature less than 200°C, to remove the intermediate substrate 304.

[0121] As shown in Figure 6F, a O₂ plasma etching is performed on the resist 305, to isolate the respective red micro-LEDs 302.

[0122] Figure 7A to 7L shows still another example for transferring a micro-LED according to the present disclosure.

[0123] As shown in Figure 7A, the original substrate 406 has resist 405 and red micro-LEDs 402 thereon. The red micro-LEDs 402 are mounted onto a UV tape 411. The UV tape 411 is located on a stiff PET support body 402. The red micro-LEDs are selectively lifted-off through laser 413.

[0124] As shown in Figure 7B, a ultraviolet is irradiated from the support body 412 side, to release un-lifted-off red micro-LEDs.

[0125] The lifted-off red micro-LEDs 402r are easily separated from the original substrate 406. As shown in Figure 7C, the lifted-off red micro-LEDs 402r are adhered on the UV tape 411, while other red micro-LEDs remain on the original substrate 406.

[0126] As shown in Figure 7D, the backup substrate 415 such as glass substrate has elastomer/polymer 416 thereon. For example, the elastomer/polymer 416 is coated on the backup substrate 415 through spin coating. For example, the elastomer/polymer 416 is PDMS or 3M LC 5320, and can be cured through ultraviolet, for exam-

ple.

[0127] As shown in Figure 7E, the support body is fully irradiated with ultraviolet, to release the red micro-LEDs and elastomer/polymer 416.

[0128] After that, for example, if the micro-LEDs do not have bumps thereon, the micro-LEDs on the backup substrate 415 can be screen-printed using silver paste.

[0129] As shown in 7F, the red micro-LEDs on the backup substrate 415 are aligned with the pads 419 on the receiving substrate 417. For example, the receiving substrate is a display substrate, and includes signal leads 418. For example, the red micro-LEDs are bonded to the pads 419 through reflow. The temperature of reflow can be more than 260°C. Then, the backup substrate 415 is separated from the receiving substrate 417 through laser lift-off.

[0130] Figure 7G shows separated receiving substrate 417. The receiving substrate 417 has pads 419 and red micro-LEDs 402r thereon.

[0131] Figure 7H shows a schematic diagram of transferring red micro-LEDs 422g from a backup substrate 420 to the receiving substrate 417. The backup substrate 420 has elastomer/polymer 421.

[0132] Figure 7I shows the separated receiving substrate 417. The receiving substrate 417 has pads 419, red micro-LEDs 402r and green micro-LEDs 402r thereon.

[0133] Figure 7J shows a schematic diagram of transferring blue micro-LEDs 425b from a backup substrate 423 to the receiving substrate 417. The backup substrate 423 has elastomer/polymer 424.

[0134] Figure 7K shows the separated receiving substrate 417. The receiving substrate 417 has pads 419, red micro-LEDs 402r, green micro-LEDs 402r and blue micro-LEDs 425b thereon

[0135] In Figure 7L, the normal subsequent processes are performed on the transferred micro-LEDs: coating polymer 426 on the receiving substrate with micro-LEDs; curing the polymer 426; etching the polymer, to expose the epitaxial layers of the micro-LEDs; forming N-metal electrodes 427 on the epitaxial layers of the micro-LEDs; and performing encapsulation (not shown) on the N-metal electrodes.

[0136] The solution of the present example, which does not form part of the claimed invention, can use both vertical micro-LEDs and lateral micro-LEDs (flip-chip micro-LEDs). The micro-LEDs of vertical structure shown in the previous figures are illustrative and do not limit the scope of the present invention, which is as defined in the appended claims. Figure 8 shows an example of lateral micro-LEDs.

[0137] In the example of Figure 8, the micro-LEDs are lateral micro-LEDs. In the lateral micro-LEDs, the P electrodes and the N electrodes thereof are located on the same side. Figure 8 shows a red lateral micro-LED 505, a green lateral micro-LED 506 and a blue lateral micro-LED 507. The red lateral micro-LED 505 contains a P electrode 505p (positive electrode) and an N electrode

505n (negative electrode). The green lateral micro-LED 506 contains a P electrode 506p and an N electrode 506n. The blue lateral micro-LED 507 contains a P electrode 507p and an N electrode 507n.

[0138] Lead structures (including pads) 515p, 515n, 516p, 516n, 517p, 517n are provided in the substrate 504. The lead structures 515p, 516p, 517p are for connection with positive electrodes. The lead structures 515n, 516n, 517n are for connection with negative electrodes.

[0139] In the example of Figure 8, the electrodes 505p, 505n, 506p, 506n, 507p, 507n are connected to the lead structures 515p, 515n, 516p, 516n, 517p, 517n via an anisotropic conductive layer 503.

[0140] Polymer 502 can be coated between the lateral micro-LEDs. A transparent cover 501 can be provided over the lateral micro-LEDs.

[0141] Figure 9 shows another example of lateral micro-LEDs. The difference between the example of Figure 9 and that of Figure 8 lies in that in Figure 9, the lateral micro-LEDs are connected to the substrate via solder rather than an anisotropic conductive layer.

[0142] Figure 9 shows a red lateral micro-LED 605, a green lateral micro-LED 606 and a blue lateral micro-LED 607. The red lateral micro-LED 605 contains a P electrode 605p and an N electrode 605n. The green lateral micro-LED 606 contains a P electrode 606p and an N electrode 606n. The blue lateral micro-LED 607 contains a P electrode 607p and an N electrode 607n.

[0143] Lead structures (including pads) 615p, 615n, 616p, 616n, 617p, 617n are provided in the substrate 604. The lead structures 615p, 616p, 617p are for connection with positive electrodes. The lead structures 615n, 616n, 617n are for connection with negative electrodes.

[0144] In the example of Figure 9, the electrodes 605p, 605n, 606p, 606n, 607p, 607n include solder bumps 602, for example. The solder bumps 602 are coated with flux, for example. The electrodes 605p, 605n, 606p, 606n, 607p, 607n are bonded to the lead structures 615p, 615n, 616p, 616n, 617p, 617n, for example, through reflow-soldering, respectively.

[0145] For example, polymer 603 can be filled between the lateral micro-LEDs and the substrate 604. A transparent cover 601 can be provided over the lateral micro-LEDs. These processes are well-known in the art and thus are not described in detail here.

[0146] Therefore, for example, the present disclosure can further include the specific application of lateral micro-LEDs. More specifically, the present disclosure further provides a method for transferring micro-LED. The method comprises: forming micro-LEDs on a laser-transparent original substrate, wherein the micro-LEDs are lateral micro-LEDs whose P electrodes and N electrodes are located on one side; bringing the P electrodes and N electrodes of the lateral micro-LEDs into contact with pads preset on a receiving substrate; and irradiating the original substrate with laser from the original substrate

side to lift-off the lateral micro-LEDs from the original substrate.

[0147] A technical effect of using lateral micro-LEDs lies in that the processing for N metal electrode after the micro-LED transfer can be omitted. Furthermore, the wafer-level color-binning/testing can be simplified because the P electrodes and N electrodes already exist when a test at wafer-level is performed.

[0148] Furthermore, for example, in this method, an anisotropic conductive layer can be provided on a receiving substrate so as to bring the P electrodes and N electrodes of the lateral micro-LEDs into contact with the pads through the anisotropic conductive layer. Then, after lifting-off the lateral micro-LEDs from the original substrate, the anisotropic conductive layer is processed to electrically connect the P electrodes and N electrodes of the lateral micro-LEDs with the pads on the receiving substrate.

[0149] For example, the anisotropic conductive layer can be at least one of an anisotropic conductive film, an anisotropic conductive paste and an anisotropic conductive tape.

[0150] In addition to bringing the P electrodes and N electrodes of the lateral micro-LEDs into contact with pads preset on a receiving substrate by the stickiness of an anisotropic conductive layer or by the surface tension of liquid (such as flux), the present disclosure can further realize the contact by actions of gravity, electrostatic force and/or electromagnetic force.

[0151] For example, when the original substrate is irradiated with laser from the original substrate side, the lateral micro-LEDs are separated from the original substrate and the lateral micro-LEDs are dropped off onto the receiving substrate because of gravity.

[0152] For example, electrostatic force can be applied by applying voltage to the pads, so that the lateral micro-LEDs are dropped off onto the receiving substrate after being lifted-off from the original substrate because of the electrostatic force.

[0153] For example, in case that the lateral micro-LEDs contains magnetic substance such as Ni, a magnetic field can be provided, so that the lateral micro-LEDs are dropped off onto the receiving substrate after being lifted-off from the original substrate because of the electromagnetic force.

[0154] Similarly, the transfer method in the example of using lateral micro-LEDs can be applied to a method for manufacturing a micro-LED device for transferring the lateral micro-LEDs onto a receiving substrate. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0155] For example, a micro-LED device, such as a display device, can be manufactured by using the manufacturing method. The micro-LED device adopts lateral micro-LEDs.

[0156] For example, the present disclosure further provides an electronic apparatus. The electronic apparatus

contains the micro-LED device. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0157] Figure 10 shows a flow chart of a method for transferring micro-LEDs by means of a contactless action according to the present disclosure.

[0158] As shown in Figure 10, in the method for transferring micro-LEDs, at step S4100, micro-LEDs are formed on a laser-transparent original substrate.

[0159] The micro-LEDs can be lateral micro-LEDs or can be micro-LEDs of vertical structure. In a lateral micro-LED, the P electrodes and N electrodes thereof are located on one same side. In a micro-LED of vertical structure, the P electrodes and N electrodes thereof are located on opposite sides.

[0160] At step S4200, the original substrate is irradiated with laser from the original substrate side to lift-off the micro-LEDs from the original substrate.

[0161] At step S4300, the micro-LEDs are brought into contact with pads preset on a receiving substrate through a contactless action.

[0162] The contactless action means that the action per se can be applied without the direct contact of objects. For example, the contactless action can be applied by means of a field. This is different from the action applied through the stickiness of an anisotropic conductive layer or by the surface tension of liquid (such as flux). It should be understood that although the contactless action per se can be applied without the direct contact of objects, the direct contact of objects can be kept through the contactless action. For example, several example of the contactless action are given as below.

[0163] For example, the contactless action is gravity. The micro-LEDs are placed over the receiving substrate. When the lift-off is performed, the micro-LEDs are dropped off on the receiving substrate and is left on the receiving substrate.

[0164] For example, the contactless action is electrostatic force. The electrostatic force can be applied by applying voltage to the pads.

[0165] For example, the contactless action is electromagnetic force. In case that the micro-LEDs contains magnetic substance, a magnetic field can be provided by means of a magnet such as permanent magnet, so that the micro-LEDs are dropped off and are left onto the receiving substrate after being lifted-off from the original substrate because of the electromagnetic force, thereby contacting with the pads directly or indirectly.

[0166] In this embodiment, the micro-LEDs are attached onto the receiving substrate via a contactless manner, which is not conceived by a person skilled in the art.

[0167] For example, the electrodes of the micro-LEDs include solder bumps. The solder bumps are bonded with the pads, for example, through reflow-soldering and so on.

[0168] The order of steps in Figure 10 will not constitute any limitation of the present invention, which is as defined in the appended claims. For example, although the step

S4200 are shown in front of the step S4030, the action of gravity, the action of electrostatic force or the action of electromagnetic force can be applied before the step S4200 or at the time when performing the step S4200. In another word, for example, the step S4300 can be performed before the step S4200 or simultaneously with the step S4200.

[0169] Similarly, the transfer method can be applied to a method for manufacturing a micro-LED device for transferring the micro-LEDs onto a receiving substrate. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0170] For example, a micro-LED device, such as a display device, can be manufactured by using the manufacturing method.

[0171] For example, the present disclosure further provides an electronic apparatus. The electronic apparatus contains the micro-LED device. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0172] Figure 11 shows a flow chart of still another illustrative embodiment of the method according to the present disclosure.

[0173] As shown in Figure 11, at step S5100, a micro-LED defect pattern on a receiving substrate is obtained.

[0174] For example, the defect pattern can be obtained through an automatic visual inspection (AVI), a photoluminescence (PL), an electro-optical test, or an electric-performance test, etc. These detection approaches are not the improvement of this disclosure and can be the prior art, and thus they are not described here in details.

[0175] At step S5200, micro-LEDs corresponding to the defect pattern are formed on a laser-transparent repair carrier substrate.

[0176] In an example, the micro-LEDs can first be mounted onto a temporary substrate in the defect pattern.

[0177] For example, the temporary substrate is rigid, such as a PET plate. For example, an adhesive, such as an UV tape, is coated on the temporary substrate. The micro-LEDs on a laser-transparent original substrate can be brought into contact with the adhesive. Then, the original substrate is irradiated with laser in the defect pattern, to lift-off the micro-LEDs from the original substrate. The lifted-off micro-LEDs in the defect pattern are kept on the temporary substrate while the un-lifted-off micro-LEDs are released through a partial adhesive releasing. After the partial adhesive releasing, the un-lifted-off micro-LEDs remain on the original substrate. The partial adhesive releasing means that after the releasing, the residual adhesion of the adhesive is sufficient to separate the lifted-off micro-LEDs from the original substrate while it cannot separate the un-lifted-off micro-LEDs from the original substrate.

[0178] Next, the micro-LEDs on the temporary substrate are transferred to the repair carrier substrate.

[0179] For example, the micro-LEDs on the temporary substrate can first be bonded onto the repair carrier substrate. The micro-LEDs on the temporary substrate can

be bonded onto the repair carrier substrate through a polymer thin film, for example. Then, the micro-LEDs is lifted-off from the temporary substrate through a complete adhesive releasing. For example, after the micro-LEDs is lifted-off from the temporary substrate, at least one part of the polymer thin film is removed, such as the polymer thin film portion between micro-LEDs.

[0180] For example, the partial adhesive releasing and the complete adhesive releasing can be performed through UV exposure.

[0181] Generally, the exposure time or energy used in the partial adhesive releasing is less than the standard exposure time or energy, i.e. the exposure time in the partial releasing is less than the standard time and/or the energy in the partial releasing is less than the standard energy. The exposure time or energy used in the complete adhesive releasing is higher than or equal to the standard exposure time or energy, i.e. the exposure time in the complete releasing is larger than or equal to the standard time and/or the energy in the complete releasing is larger than or equal to the standard energy. The standard exposure time or energy can be the exposure time or energy just releasing the adhesive completely, or can be the nominal exposure time or energy.

[0182] At step S5300, the micro-LEDs on the repair carrier substrate are aligned with the defect positions on the receiving substrate, and the micro-LEDs are brought into contact with the pads at the defect positions.

[0183] At step S5400, the repair carrier substrate is irradiated with laser from the repair carrier substrate side, to lift-off the micro-LEDs from the repair carrier substrate.

[0184] For example, the repair carrier substrate is a sapphire substrate. As described above, in the present disclosure, the substrate adopted is laser-transparent.

That is, compared with the device such as a micro-LED to be lifted off, the substrate is transparent with respect to the laser to be irradiated, i.e. the substrate has a higher transmittance. Accordingly, the energy in the laser will be mainly absorbed by the device (such as a micro-LED) behind it when it is irradiated, to achieve the lift-off. Of course, the larger the transmittance difference between the laser-transparent substrate and the device is, the better the lift-off effect is.

[0185] In another embodiment, the present disclosure further provides a method for manufacturing a micro-LED device. The manufacturing method comprises repairing micro-LED defects on a receiving substrate by using the method for repairing micro-LED defects according to this embodiment. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0186] In another embodiment, the present disclosure further provides a micro-LED device, such as a display device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device according to said embodiment.

[0187] In another embodiment, the present disclosure further provides an electronic apparatus. The electronic

apparatus contains a micro-LED device according to the embodiment. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0188] After micro-LEDs of large scale are transferred to a receiving substrate, a yield loss to a certain degree will arise. Thus, a repair is necessary at most cases to guarantee the product quality. In the prior art, a pick-up head is used to perform the repair. The repair approach of the prior is relatively complicated and the efficiency thereof is relatively low. The repair approach of this disclosure is relatively simple and/or has a relatively high efficiency.

[0189] Figures 12A to 12F show an example for repairing micro-LED defects according to the present disclosure.

[0190] As shown in Figure 12A, micro-LEDs 703 are formed on an original substrate 701. The micro-LEDs 703 include defect micro-LEDs and good micro-LEDs. The micro-LEDs are mounted onto a temporary substrate 705 through an adhesive layer 704. The adhesive layer 704 is an UV tape for example. The temporary substrate 705 is a PET plate, for example. The original substrate 701 is irradiated with laser 702 in a defect pattern, to lift off the defect micro-LEDs from the original substrate.

[0191] As shown in Figure 12B, the adhesive layer (the UV tape) 704 is partially exposed with an ultra violet radiation 706 from the side of the temporary substrate 705.

[0192] As shown in Figure 12C, after the partial exposure, the adhesive layer 704 still remain a certain residual stiction sufficient to separate the laser-lifted-off micro-LEDs 703b from the original substrate, while leaving the un-laser-lifted-off micro LEDs 703a on the original substrate. Since the micro-LEDs are lifted off with laser in the defect pattern, the adhesive layer 704 (or the temporary substrate 705) has good micro-LEDs arranged in the defect pattern thereon.

[0193] As shown in Figure 12D, the micro-LEDs 703b on the adhesive layer 704 are temporarily bonded onto a repair carrier substrate 707 through a polymer thin film 708. Then, the adhesive layer 704 is completely exposed. As shown in Figure 12E, the adhesive layer 704 is separated from the micro-LEDs 703b. Figure 12F shows the repair carrier substrate 707 and the micro-LEDs 703b in the defect pattern thereon for repairing. As shown in Figure 12F, the bonding polymer thin film 708 between the micro-LEDs 703b can be removed, leaving the thin film portions between the micro-LEDs 703b and the substrate 707.

[0194] Next, the repair carrier substrate 707 can be used for repairing the defects on a receiving substrate by means of laser lifting-off.

[0195] Figure 13 shows a flow chart of the method for pre-screening defect micro-LEDs of still another illustrative embodiment according to the present disclosure.

[0196] As shown in Figure 13, at step S6100, a defect pattern of defect micro-LEDs on a laser-transparent substrate is obtained.

[0197] For example, the defect pattern can be obtained

through an automatic visual inspection, a photoluminescence, an electro-optical test, or an electric-performance test.

[0198] At step S6200, the laser-transparent substrate is irradiated with laser from the laser-transparent substrate side in accordance with the defect pattern, to lift-off the defect micro-LEDs from the laser-transparent substrate.

[0199] In an example, an action is applied through a contact manner to separate the lifted-off micro-LEDs from the laser-transparent substrate. For example, the micro-LEDs on the laser-transparent substrate can be mounted onto an UV tape. For example, the UV tape is attached on a rigid support body. The defect micro-LEDs are lifted-off through laser to the UV tape and the non-defect micro-LEDs are kept on the laser-transparent substrate though an UV exposure.

[0200] In another example, the defect micro-LEDs can be lifted-off from the laser-transparent substrate through a contactless action. As described above, the contactless action is applied without contact. For example, the contactless action is at least one of gravity, electrostatic force and electromagnetic force. These actions can be applied according to the manner described above.

[0201] According to the present disclosure, a repair can be performed after the micro-LEDs are transferred to the receiving substrate, or a repair can be performed on the laser-transparent substrate before the transfer. For example, good micro-LEDs are formed at the position of the lifted-off micro-LEDs on the laser-transparent substrate. The good micro-LEDs can be formed at the defect positions by using the repairing method described above.

[0202] In another embodiment, the present disclosure further provides a method for manufacturing a micro-LED device. The manufacturing method comprises pre-screening defect micro-LEDs defects on a laser-transparent substrate by using the method for prescreening defect micro-LEDs according to this embodiment. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0203] In another embodiment, the present disclosure further provides a micro-LED device, such as a display device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device according to said embodiment.

[0204] In another embodiment, the present disclosure further provides an electronic apparatus. The electronic apparatus contains a micro-LED device according to the embodiment. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0205] In the prior art, both good micro-LEDs and defect micro-LEDs on a substrate are transferred to a receiving substrate during the transfer. However, according to the solution of this disclosure, only known-good micro-LEDs are transferred to the receiving substrate.

[0206] Figures 14A to 14C show an example for pre-screening defect micro-LEDs according to the present

disclosure.

[0207] In this example, the defect pattern on a laser-transparent substrate is obtained through an automatic visual inspection (AVI), a photoluminescence (PL), an electro-optical test, or an electric-performance test, etc. Then, the laser-transparent substrate is mounted onto a UV tape. As shown in Figure 14A, the UV tape 804 is placed on a support body 805. The laser-transparent substrate 801 is mounted onto the UV tape 804 via micro-LEDs 803. The substrate 801 is irradiated with laser in the defect pattern, to lift off the defect micro-LEDs from the substrate 801.

[0208] As shown in Figure 14B, the UV tape 804 is partially exposed with an ultra violet radiation 806 from the side of the support body 805.

[0209] As shown in Figure 14C, after the partial exposure, the UV tape 804 still remains a certain residual stiction sufficient to separate the laser-lifted-off micro-LEDs 803b from the substrate 801, while leaving the un-laser-lifted-off micro-LEDs 803a on the substrate 801.

[0210] Figures 15A to 15B show another example for pre-screening defect micro-LEDs according to the present disclosure.

[0211] As shown in Figure 15A, the substrate (wafer) 901 has good micro-LEDs 902 and defect micro-LEDs 903 thereon. The defect micro-LEDs 903 are pre-screened before the micro-LEDs are transferred from the substrate 901 to a receiving substrate (not shown), by means of the method of this disclosure. Figure 15B shows the substrate 901 after the defect micro-LEDs are pre-screened.

[0212] Figures 16A to 16B is an enlarged view of the area "A" of Figure 15B. As shown in Figure 16A, the defect micro-LED at the position 903a is pre-screened. As shown in Figure 16B, a repair can be performed directly on the substrate 901, to form a good micro-LED at the position 903a. Alternatively, the repair can be performed after the micro-LEDs are transferred from the substrate 901 to a receiving substrate.

[0213] Figure 17 shows a flow chart of still another illustrative embodiment of the method for transferring micro-LED at wafer level according to the present disclosure.

[0214] As shown in Figure 17, at step S7100, micro-LEDs on a laser-transparent original substrate are temporarily bonded onto a carrier substrate via a first bonding layer.

[0215] For example, the first bonding layer can be a UV or light releasable tape. For example, the carrier substrate can be a PET plate. The PET plate is rigid and can provide a sufficient support to the UV or light releasable tape to prevent a displacement of the transferred micro-LEDs.

[0216] At step S7200, the original substrate is irradiated from the original substrate side with laser, to lift-off selected micro-LEDs from the original substrate.

[0217] At step S7300, a partial release is performed on the first bonding layer, to transfer the selected micro-

LEDs to the carrier substrate.

[0218] For example, the release degree of the first bonding layer can be controlled by controlling the intensity and/or the irradiation time of the UV or light irradiating the first bonding layer.

[0219] In an example, in order to sufficient guarantee the transfer of the lifted-off micro-LEDs onto the carrier substrate, a contactless action can be applied onto the micro-LEDs during the partial release. For example, the contactless action is at least one of gravity, electrostatic force and electromagnetic force.

[0220] At step S7400, the micro-LEDs on the carrier substrate are temporarily bonded onto a transfer head substrate via a second bonding layer.

[0221] At step S7500, a full release is performed on the first bonding layer, to transfer the micro-LEDs to the transfer head substrate.

[0222] For example, the partial release and the full release are performed by exposure using UV or light.

[0223] At step S7600, the micro-LEDs on the transfer head substrate is bonded onto a receiving substrate.

[0224] At step S7700, the transfer head substrate is removed by releasing the second bonding layer, to transfer the micro-LEDs to the receiving substrate.

[0225] For example, the second bonding layer can be released by a thermal release.

[0226] In an example, the transferred micro-LEDs are vertically structured. The vertically-structured micro-LEDs can provide a display panel with a higher resolution. The vertically-structured micro-LEDs are un-finished micro-LEDs. So, after the micro-LEDs are transferred to the receiving substrate, N electrodes are formed on the micro-LEDs on the receiving substrate and an encapsulation is performed on the N electrodes, to form complete micro-LEDs.

[0227] In order to improve the yield of the display panel, the micro-LEDs can be arranged on the receiving substrate in a redundant manner.

[0228] In another embodiment, the present disclosure further provides a method for manufacturing a micro-LED device. The manufacturing method comprises transferring micro-LEDs onto a receiving substrate of the micro-LED device by using the method for transferring micro-LED at wafer level according to this embodiment. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0229] In another embodiment, the present disclosure further provides a micro-LED device, such as a display device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device according to said embodiment.

[0230] In another embodiment, the present disclosure further provides an electronic apparatus. The electronic apparatus contains a micro-LED device according to the embodiment. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0231] Figures 18A to 18J show an example for trans-

ferring micro-LEDs at wafer level according to the present disclosure.

[0232] As shown in Figure 18A, micro-LEDs are formed on a laser-transparent original substrate 1001. Figure 18A shows red micro-LEDs 1003r. The original substrate 1001 is a sapphire substrate, for example.

[0233] The micro-LEDs 1003r are temporarily bonded onto a carrier substrate 1005 via a first bonding layer 1004. For example, the first bonding layer 1005 can be a UV or light releasable tape. For example, the carrier substrate can be a PET plate.

[0234] In Figure 18A, the original substrate 1001 is irradiated from the original substrate side with laser 1002, to lift-off selected micro-LEDs from the original substrate.

[0235] In Figure 18B, a partial release is performed on the first bonding layer 1004. As shown in Figure 18C, the selected micro-LEDs 1003r are transferred to the carrier substrate 1005.

[0236] For example, the release degree of the first bonding layer 1004 can be controlled by controlling the intensity and/or the irradiation time of the UV or light 1006 irradiating the first bonding layer.

[0237] In order to improve the effect of the release, a contactless action can be applied onto the micro-LEDs during the partial release. For example, the contactless action is at least one of gravity, electrostatic force and electromagnetic force.

[0238] Next, in Figure 18D, the micro-LEDs 1003r are temporarily bonded onto a transfer head substrate 1008 via a second bonding layer 1007.

[0239] In Figure 18E, a full release is performed on the first bonding layer 1004. In Figure 18F, the micro-LEDs 1003r are transferred to the transfer head substrate 1008.

[0240] For example, the partial release and the full release can be performed by exposure using UV or light.

[0241] Figures 18G and 18H show a transfer head substrate 1010 and a transfer head substrate 1012, respectively. The transfer head substrate 1010 has green micro-LEDs 1003g and a second bonding layer 1009. The transfer head substrate 1012 has blue micro-LEDs 1003b and a second bonding layer 1011.

[0242] In Figure 18I, the micro-LEDs 1003r on the transfer head substrate is bonded onto a receiving substrate 1013 for finishing the transfer.

[0243] In Figure 18J, the second bonding layer is released and the transfer head substrate is removed. The red, green and blue micro-LEDs 1003r, 1003g, 1003b are transferred to the receiving substrate 1013.

[0244] For example, the second bonding layer can be released by a thermal release.

[0245] The above micro-LEDs can be vertically structured. So, after the micro-LEDs are transferred to the receiving substrate 1013, N electrodes are formed on the micro-LEDs and an encapsulation is performed on the N electrodes, to form complete micro-LEDs (not shown).

[0246] Figure 19 shows a flow chart of an illustrative embodiment of the method for transferring micro-LED according to the present invention.

[0247] As shown in Figure 19, at step S8100, a mask layer is formed on the backside of a laser-transparent original substrate, wherein micro-LEDs are formed on the front-side of the original substrate.

[0248] For example, the original substrate can be a sapphire substrate. The thickness range of the original substrate can 20-1000 μ m, or 50-500 μ m, or 100-300 μ m.

[0249] In this embodiment, the mask layer is used to selectively lift-off micro-LEDs, which can provide a relatively high display resolution. In the prior art, the display resolution is normally larger than 50 μ m. For example, according to this invention, the spatial resolution range of the mask layer can be 1-50 μ m.

[0250] For example, the material of the mask layer is selected from photoresist, polymer, metal/metal compound, metal/metal alloy, metal/metal composite, silicon and silicide.

[0251] For example, the micro-LEDs can be vertical micro-LEDs or can be lateral micro-LEDs.

[0252] At step S8200, the micro-LEDs on the original substrate is brought into contact with preset pads on a receiving substrate.

[0253] For example, the micro-LEDs are in contact with the pad through micro-bump bonding. The micro-bump bonding can be solder, alloy, metal, paste, adhesive, ink, etc.

[0254] At step S8300, the original substrate is irradiated from the original substrate side with laser through the mask layer, to lift-off micro-LEDs from the original substrate.

[0255] For example, during the micro-LEDs is lifted-off from the original substrate, a contactless action is applied onto the micro-LEDs to ensure the lift-off of the micro-LEDs. For example, the contactless action is at least one of gravity, electrostatic force and in the invention as claimed, the contactless action is an electromagnetic force.

[0256] In this invention, since a mask layer is used to select micro-LEDs to be lifted-off, the control of laser beams can be simplified. For example, it is unnecessary to control the laser to select micro-LEDs to be lifted-off. Furthermore, in this invention, it is unnecessary to use a laser with small beam size to improve the resolution and thus the requirement for laser beam size is lowered. In an example, the usage of a relatively large laser beam can improve the lifting-off speed. For example, the laser beam size of the laser is 50-5000 μ m.

[0257] In an example, the micro-LEDs can be arranged on the receiving substrate in a redundant manner to improve the yield of production.

[0258] In another embodiment, the present invention further provides a method for manufacturing a micro-LED device. The manufacturing method comprises transferring micro-LEDs onto a receiving substrate of the micro-LED device by using the method for transferring micro-LED according to this embodiment. For example, the receiving substrate is a display screen or display substrate. The micro-LED device is a display device, for example.

[0259] In another embodiment, the present disclosure further provides a micro-LED device, such as a display device. The micro-LED device can be manufactured by using the method for manufacturing a micro-LED device according to said embodiment.

[0260] In another embodiment, the present disclosure further provides an electronic apparatus. The electronic apparatus contains a micro-LED device according to the embodiment. For example, the electronic apparatus can be a mobile phone, a pad and so on.

[0261] Figures 20A to 20I show another example for transferring micro-LED according to the present invention.

[0262] As shown in Figure 20A, the substrate 1102r such as a sapphire substrate has red micro-LEDs on its front-side and has a mask 1101r on its backside. A receiving substrate 1106 is provided with leads and pads 1105. For example, solder 1104 is provided on the pads corresponding to the micro-LEDs to be lifted-off.

[0263] As shown in Figure 20B, the red micro-LEDs 1103r are brought into contact with pads 1105 through the solder 1104. A laser 1107r is used to irradiate the substrate 1102r through the mask 1101r, to lift-off the red micro-LEDs 1103r. In this procedure, a contactless action, such as gravity, electrostatic force, and in the claimed invention an electromagnetic force is applied onto the micro-LEDs 1103r, to guarantee a complete lift-off.

[0264] As shown in Figure 20C, the red micro-LEDs are transferred onto the receiving substrate 1106.

[0265] Figures 20D and 20E show the procedure of transferring green micro-LEDs. As shown in Figure 20D, a laser 1107g is used to irradiate a substrate 1102g through a mask 1101g to lift-off green micro-LEDs 1103g. Figure 20E shows the receiving substrate 1106 after the lifting-off.

[0266] Figures 20F and 20G show the procedure of transferring blue micro-LEDs. As shown in Figure 20F, a laser 1107b is used to irradiate a substrate 1102b through a mask 1101b to lift-off blue micro-LEDs 1103b. Figure 20G shows the receiving substrate 1106 after the lifting-off.

[0267] Post processing can be done on the receiving substrate 1106 after the transfer. For example, the micro-LEDs can be vertical micro-LEDs. As shown in Figure 20H, polymer 1108 is coated on the micro-LEDs 1103r, 1103g, 1103b, to protect the micro-LEDs. The polymer 1108 is etched to expose the epitaxial layers of the micro-LEDs. As shown in Figure 20I, N-metal electrodes are formed on the epitaxial layers of the micro-LEDs to finish the micro-LEDs.

[0268] Although some specific embodiments of the present invention have been demonstrated in detail with examples, it should be understood by a person skilled in the art that the above examples are only intended to be illustrative but not to limit the scope of the present invention. It should be understood by a person skilled in the art that the above embodiments can be modified without departing from the scope of the present invention. The

scope of the present invention is defined by the attached claims.

5 Claims

1. A method for transferring micro-LEDs, comprising:

forming a mask layer (1101r, 1101g, 1101b) on the backside of a laser-transparent original substrate (1102r, 1102g, 1102b), wherein micro-LEDs (1103r, 1103g, 1103b) are formed on the front-side of the original substrate (1102r, 1102g, 1102b);

bringing the micro-LEDs on the original substrate in contact with preset pads (1105) on a receiving substrate (1106); and

irradiating the original substrate from the original substrate side with laser (1107r, 1107g, 1107b) through the mask layer, to lift-off micro-LEDs from the original substrate,

wherein during the micro-LEDs (1103r, 1103g, 1103b) are lifted-off from the original substrate (1102r, 1102g, 1102b), a contactless action is applied onto the micro-LEDs, and the contactless action is electromagnetic force.

2. The method according to claim 1, wherein the original substrate (1102r, 1102g, 1102b) is a sapphire substrate, and the thickness range of the original substrate is 20-1000 μ m, or 50-500 μ m, or 100-300 μ m.

3. The method according to claim 1, wherein the spatial resolution range of the mask layer (1101r, 1101g, 1101b) is 1-50 μ m.

4. The method according to claim 1, wherein the material of the mask layer (1101r, 1101g, 1101b) is selected from photoresist, polymer, metal/metal compound, metal/metal alloy, metal/metal composite, silicon and silicide.

5. The method according to claim 1, wherein the micro-LEDs are in contact with the pad through micro-bump bonding.

6. The method according to claim 1, wherein the laser beam size of the laser (1107r, 1107g, 1107b) is 50-5000 μ m.

7. The method according to claim 1, wherein the micro-LEDs (1103r, 1103g, 1103b) are arranged on the receiving substrate in a redundant manner.

8. A method for manufacturing a micro-LED device, **characterized by** comprising transferring micro-LEDs onto a receiving substrate of the micro-LED

device by using the method according to claim 1.

Patentansprüche

1. Verfahren zum Übertragen von Mikroleuchtdioden, umfassend:

Ausbilden einer Maskenschicht (1101r, 1101g, 1101b) auf der Rückseite eines lasertransparenten Originalsubstrats (1102r, 1102g, 1102b), wobei die Mikroleuchtdioden (1103r, 1103g, 1103b) auf der Vorderseite des Originalsubstrats (1102r, 1102g, 1102b) ausgebildet sind; Inkontaktbringen der Mikroleuchtdioden auf dem Originalsubstrat mit voreingestellten Unterlagen (1105) auf einem Empfangssubstrat (1106); und Bestrahlen des Originalsubstrats von der Seite des Originalsubstrats mit einem Laser (1107r, 1107g, 1107b) durch die Maskenschicht, um die Mikroleuchtdioden vom Originalsubstrat abzutrennen, während die Mikroleuchtdioden (1103r, 1103g, 1103b) vom Originalsubstrat (1102r, 1102g, 1102b) abgetrennt werden, wird eine berührungslose Wirkung auf die Mikroleuchtdioden ausgeübt, und wobei die berührungslose Wirkung eine elektromagnetische Kraft ist.

2. Verfahren nach Anspruch 1, wobei das Originalsubstrat (1102r, 1102g, 1102b) ein Saphirsubstrat ist und der Dickenbereich des Originalsubstrats 20-1000 μm oder 50-500 μm oder 100-300 μm ist.
3. Verfahren nach Anspruch 1, **dadurch gekennzeichnet, dass** der räumliche Auflösungsbereich der Maskenschicht (1101r, 1101g, 1101b) 1-50 μm ist.
4. Verfahren nach Anspruch 1, wobei das Material der Maskenschicht (1101r, 1101g, 1101b) ausgewählt ist aus Photoresist, Polymer, Metall/Metall-Verbindung, Metall/Metall-Legierung, Metall/Metall-Verbundwerkstoff, Silizium und Silizid.
5. Verfahren nach Anspruch 1, wobei die Mikroleuchtdioden durch Mikro-Bump-Verbindung mit der Unterlage in Kontakt stehen.
6. Verfahren nach Anspruch 1, wobei die Laserstrahlgröße des Lasers (1107r, 1107g, 1107b) 50-5000 μm beträgt.
7. Verfahren nach Anspruch 1, wobei die Mikroleuchtdioden (1103r, 1103g, 1103b) redundant auf dem Empfangssubstrat angeordnet sind.

8. Verfahren zur Herstellung einer Mikroleuchtdiodenvorrichtung, **gekennzeichnet durch** das Übertragen von Mikroleuchtdioden auf ein Empfangssubstrat der Mikroleuchtdiodenvorrichtung unter Verwendung des Verfahrens nach Anspruch 1.

Revendications

1. Procédé de transfert des diodes électroluminescentes, comprenant:

Former une couche de masque (1101r, 1101g, 1101b) sur la surface arrière d'un substrat d'origine transparent au laser (1102r, 1102g, 1102b), dans lequel des diodes électroluminescentes (1103r, 1103g, 1103b) sont formées sur la surface avant du substrat d'origine (1102r, 1102g, 1102b);

Amener les diodes électroluminescentes sur le substrat d'origine en contact avec des pads prédéfinis (1105) sur un substrat de réception (1106); et

Irradier le substrat d'origine du côté du substrat d'origine avec un laser (1107r, 1107g, 1107b) à travers la couche de masque, afin de décoller les diodes électroluminescentes du substrat d'origine, dans lequel, lorsque les diodes électroluminescentes (1103r, 1103g, 1103b) sont décollées du substrat d'origine (1102r, 1102g, 1102b), une force sans contact est appliquée sur lesdites diodes électroluminescentes et ladite force sans contact est une force électromagnétique.

2. Procédé selon la revendication 1, dans lequel le substrat d'origine (1102r, 1102g, 1102b) est un substrat en saphir et l'épaisseur du substrat d'origine est comprise entre 20 et 1000 μm , ou entre 50 et 500 μm ou entre 100 et 300 μm .
3. Procédé selon la revendication 1, dans lequel la gamme de résolution spatiale de la couche de masque (1101r, 1101g, 1101b) est comprise entre 1 et 50 μm .
4. Procédé selon la revendication 1, dans lequel le matériau de ladite couche de masque (1101r, 1101g, 1101b) est choisi parmi un ré sine photosensible, un polymère, un métal / composé métal, un métal / alliage métal, un métal / composite métal, du silicium et du siliciure.
5. Procédé selon la revendication 1, dans lequel lesdites diodes électroluminescentes sont en contact avec lesdits pads par liaison microconvexe adhérente.

6. Procédé selon la revendication 1, dans lequel la taille du faisceau dudit laser (1107r, 1107g, 1107b) est de 50-5000 m.
7. Procédé selon la revendication 1, dans lequel les diodes électroluminescentes (1103r, 1103g, 1103b) sont agencées sur le substrat de réception de manière redondante. 5
8. Procédé de fabrication d'un dispositif à diode électroluminescente comprenant l'utilisation du procédé selon la revendication 1 pour transférer des diodes électroluminescentes à un substrat de réception d'un dispositif à diode électroluminescente. 10

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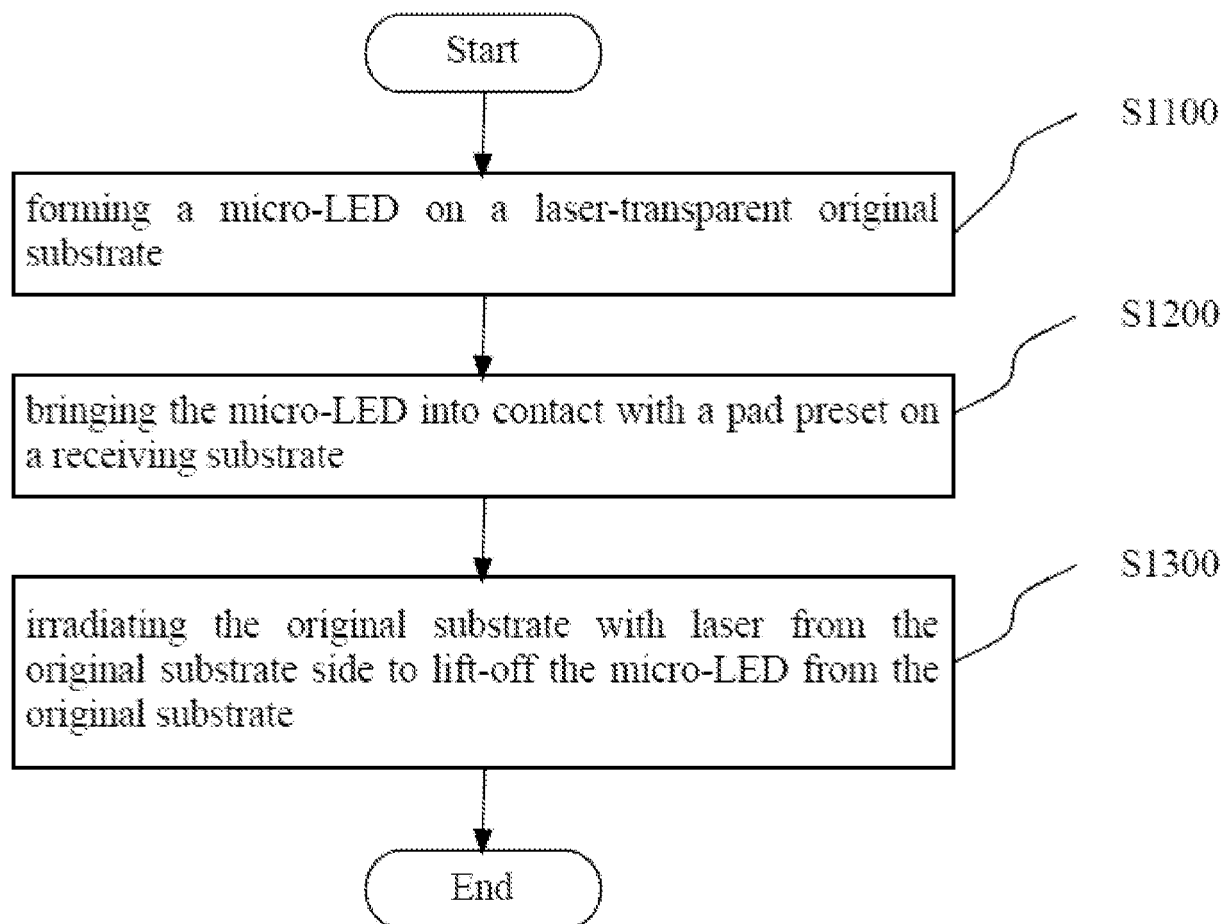


FIG. 1

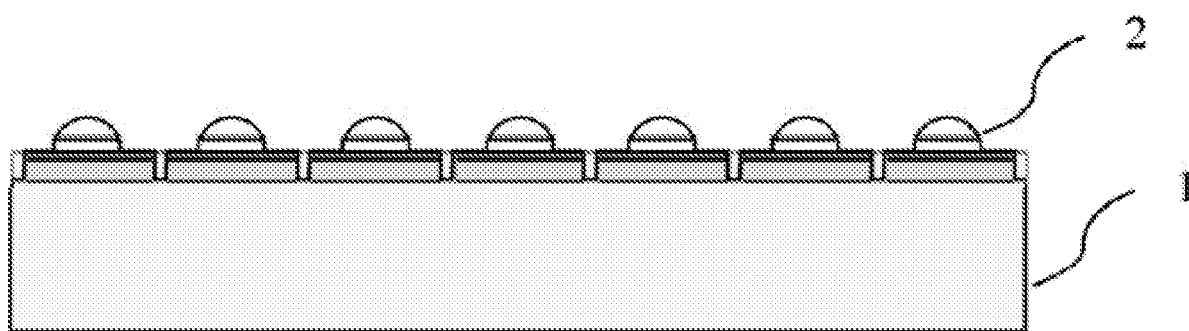


FIG. 2A

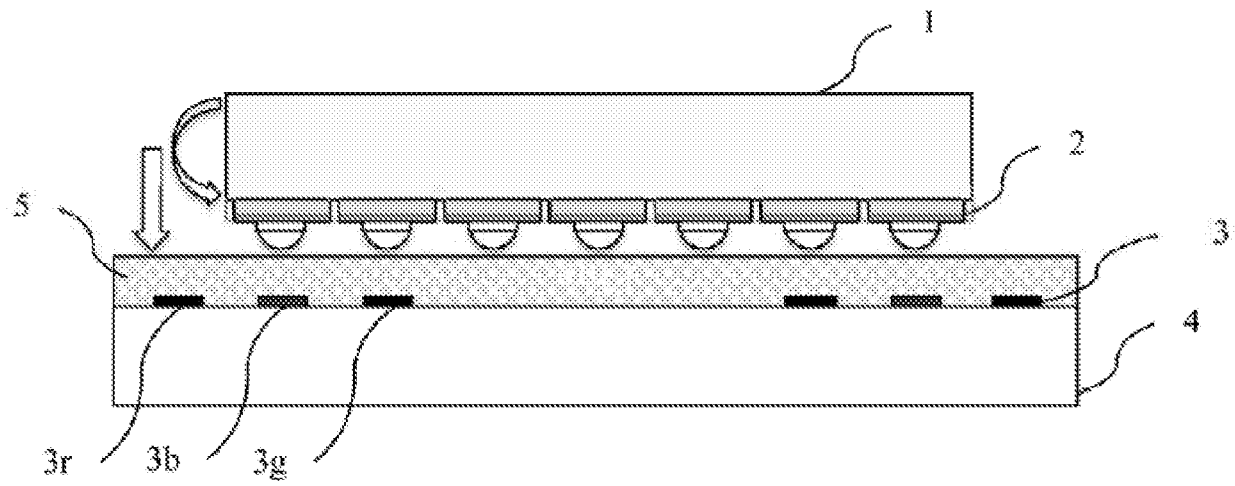


FIG. 2B

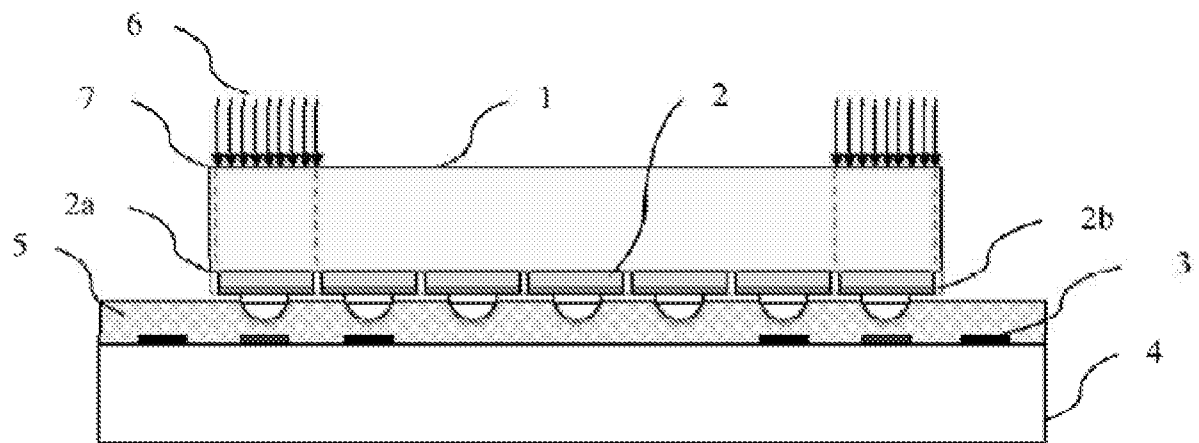


FIG. 2C

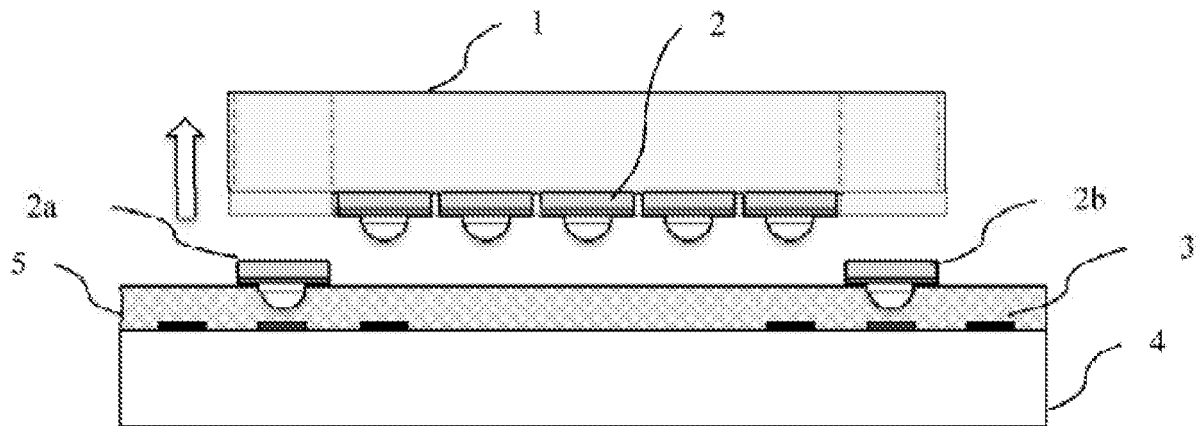


FIG. 2D

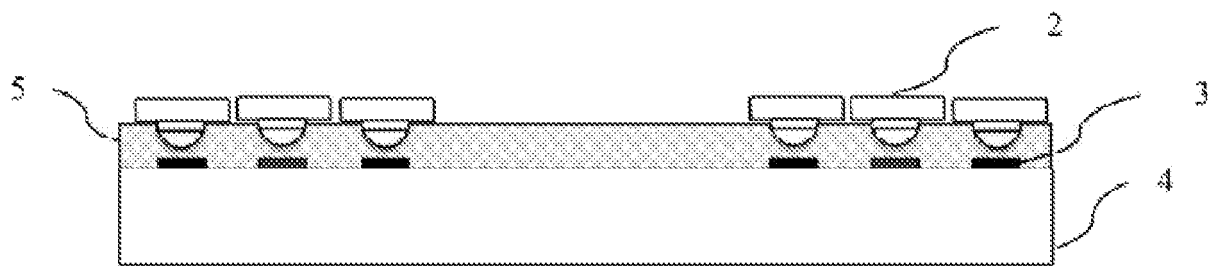


FIG. 2E

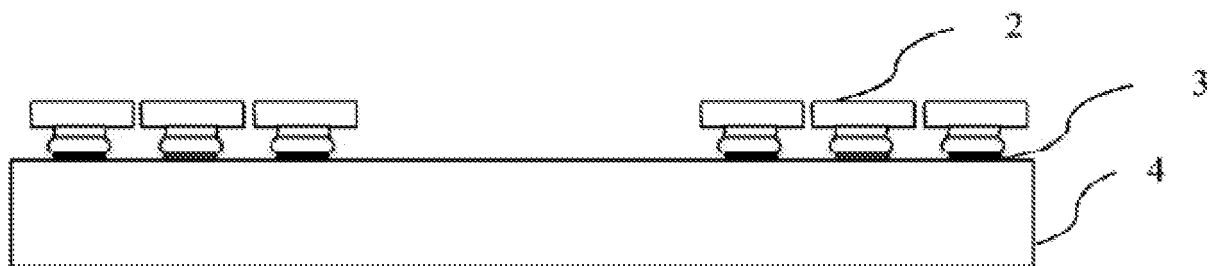


FIG. 2F

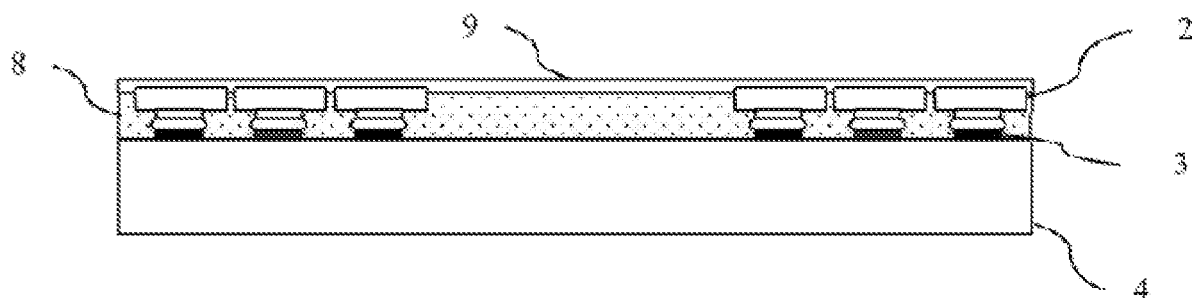


FIG. 2G

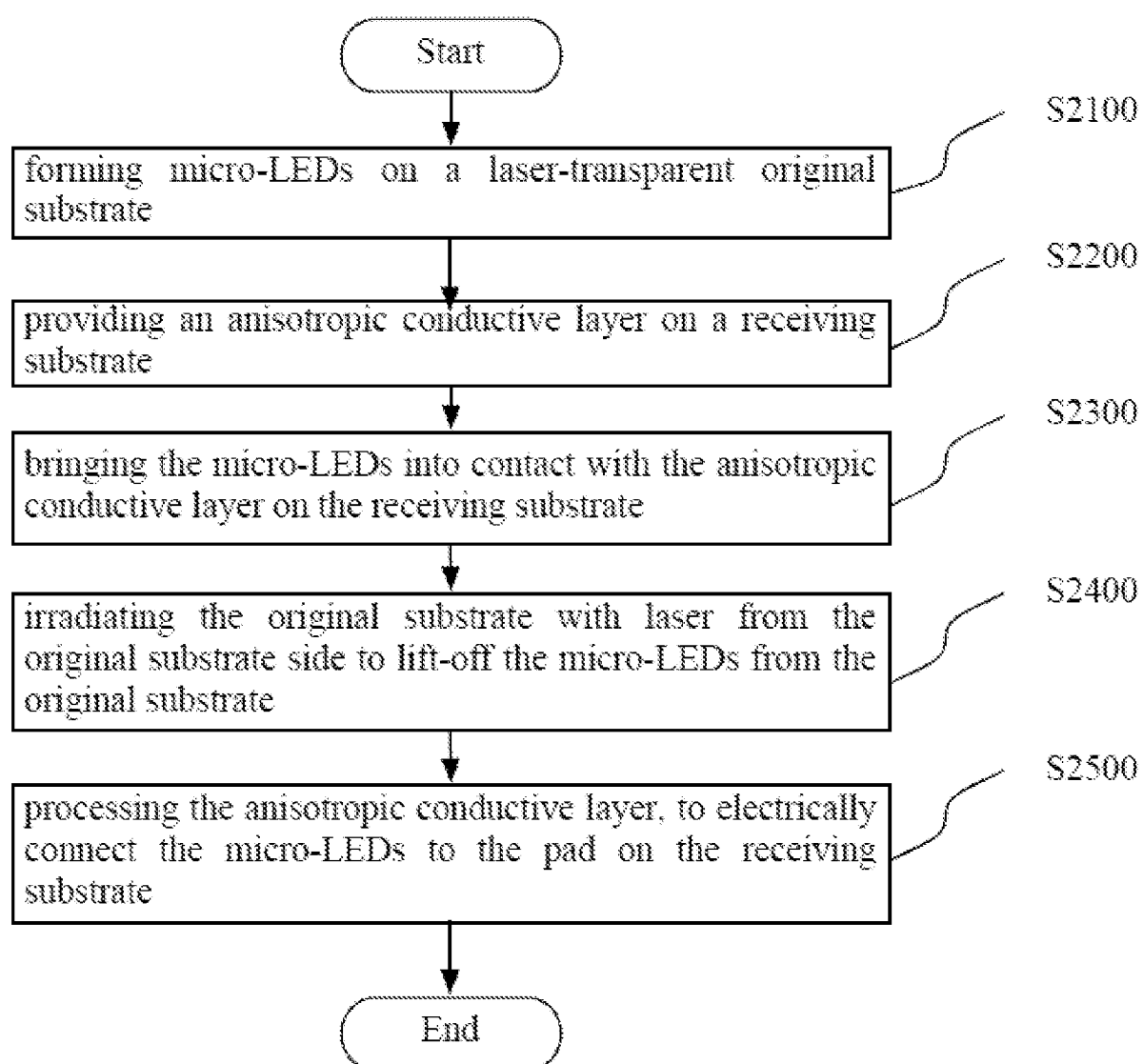


FIG. 3

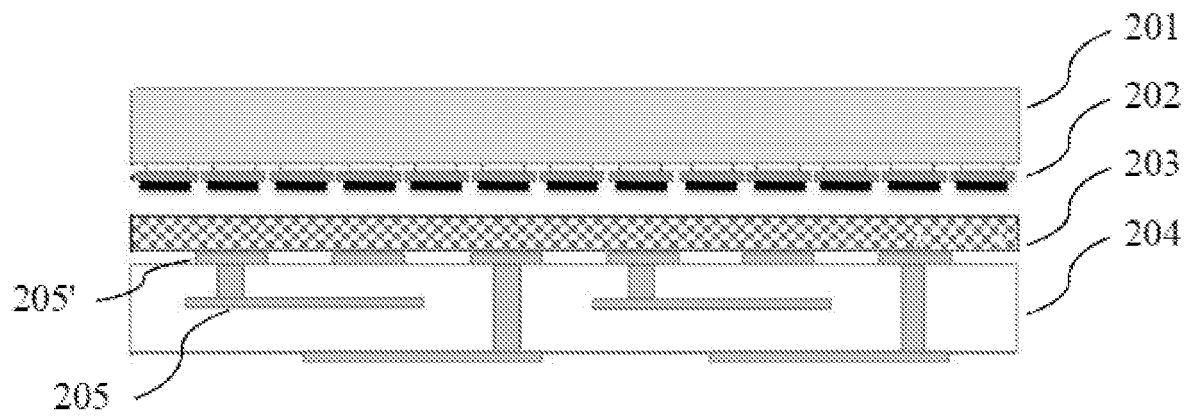


FIG. 4A

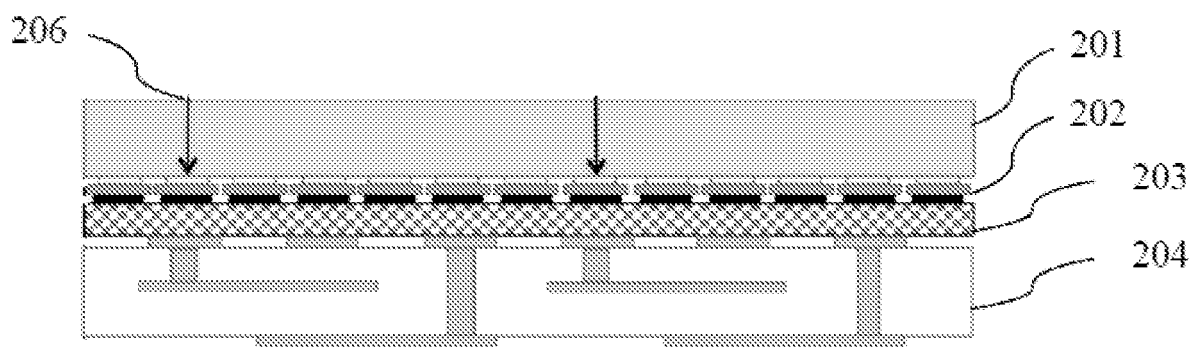


FIG. 4B

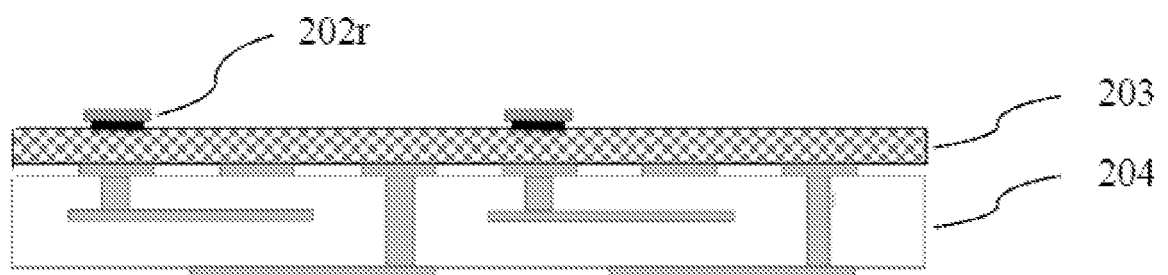


FIG. 4C

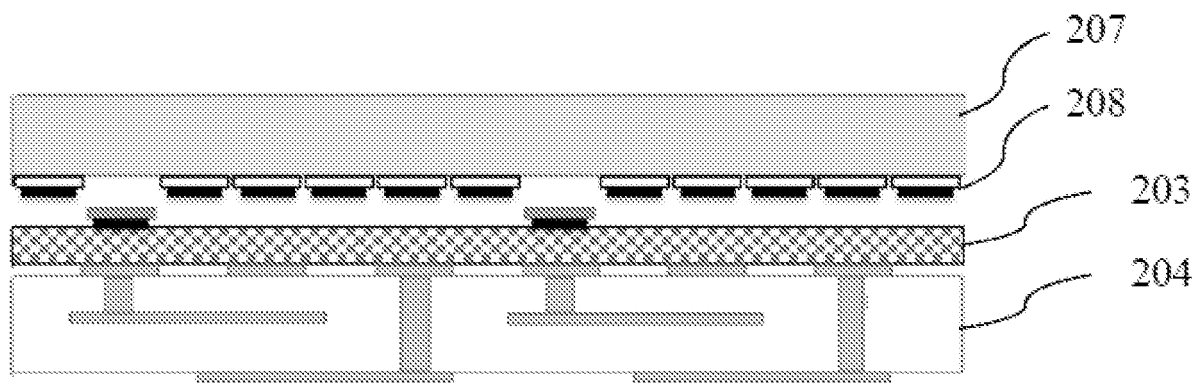


FIG. 4D

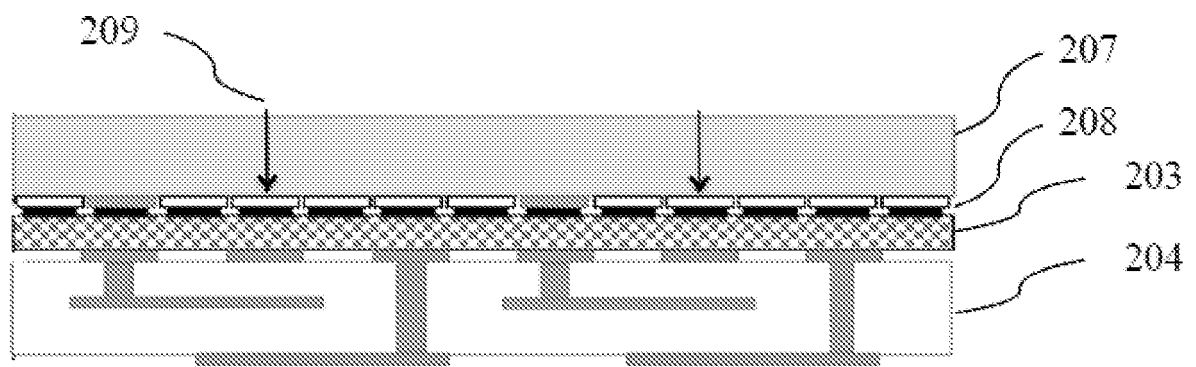


FIG. 4E

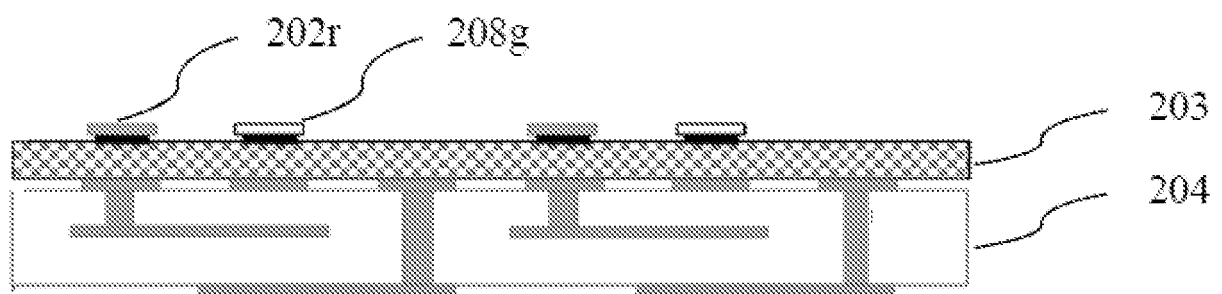


FIG. 4F

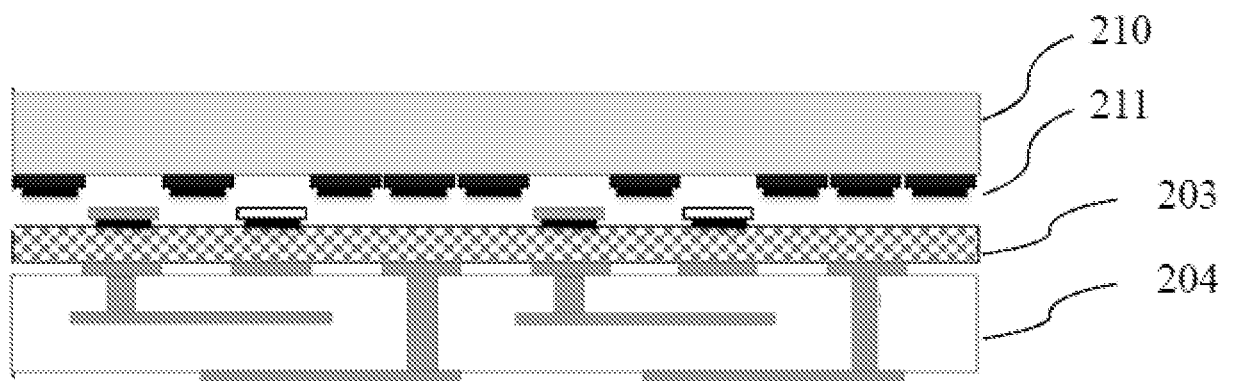


FIG. 4G

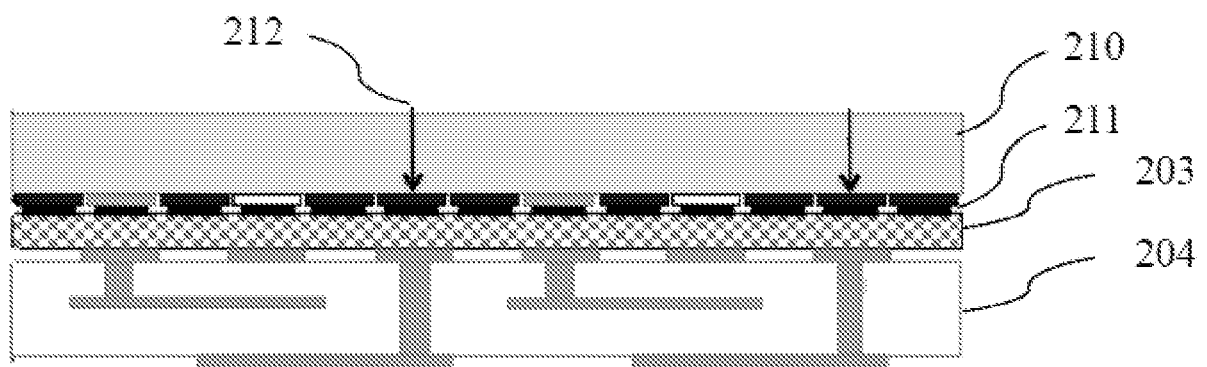


FIG. 4H

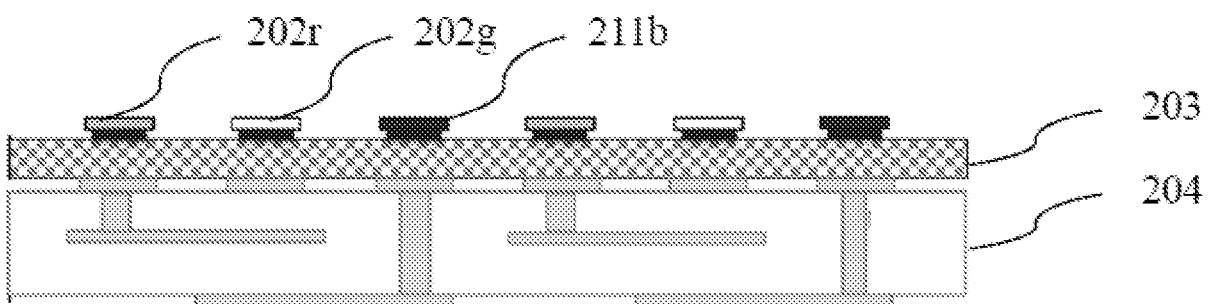


FIG. 4I

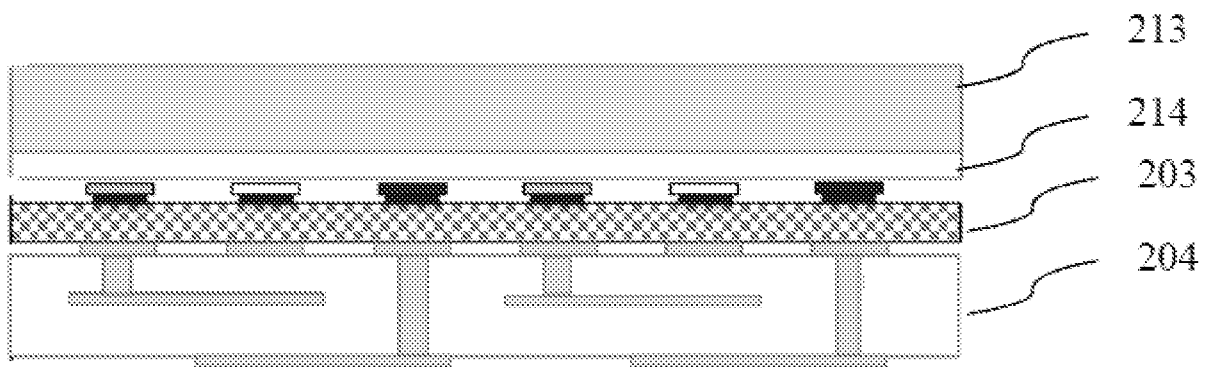


FIG. 4J

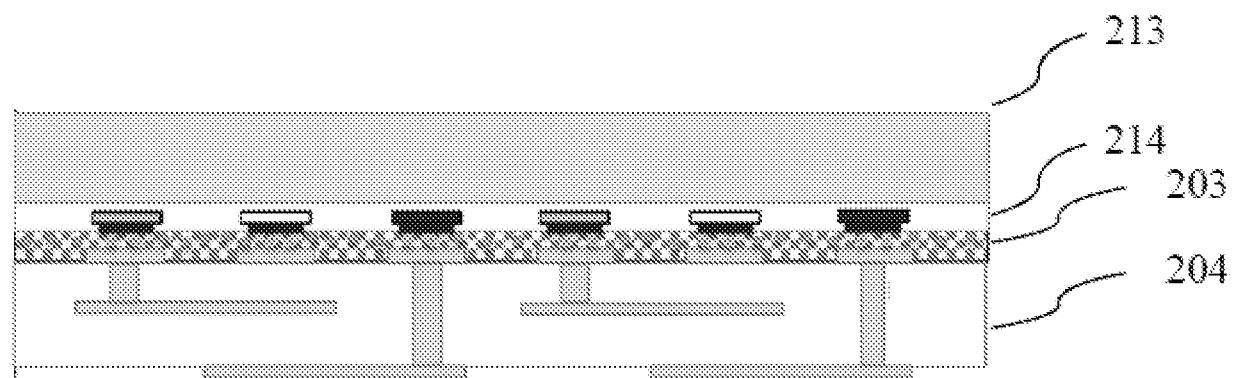


FIG. 4K

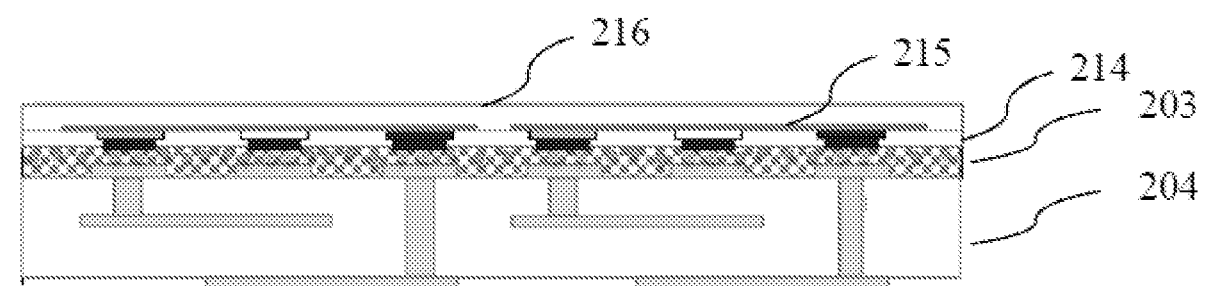


FIG. 4L

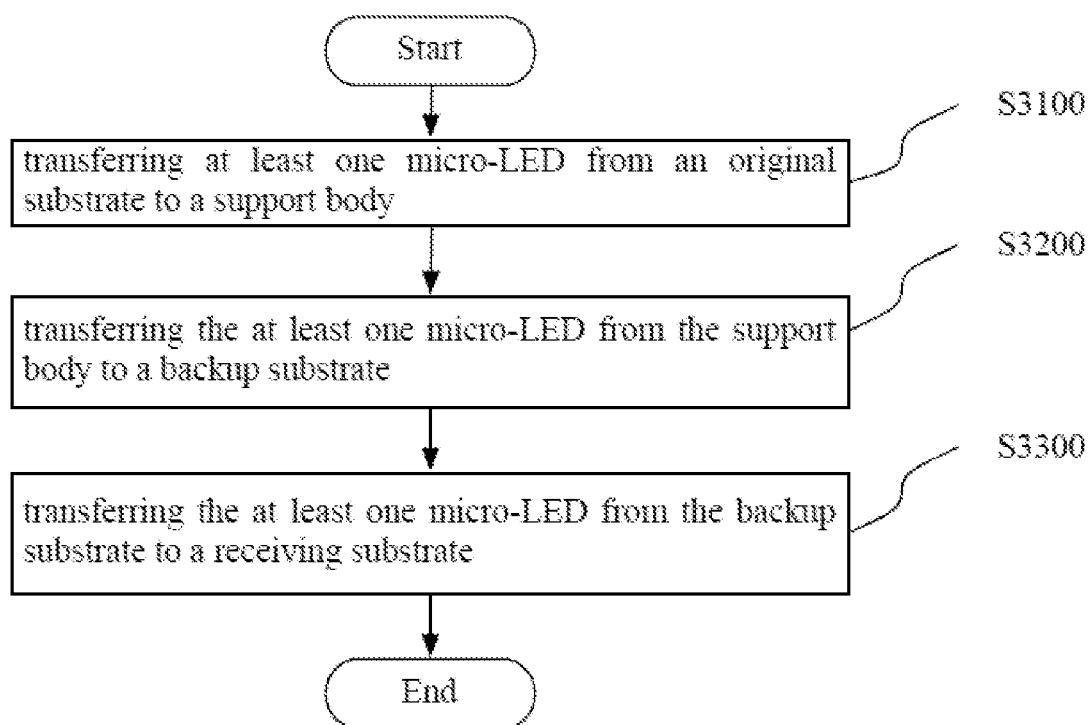


FIG. 5

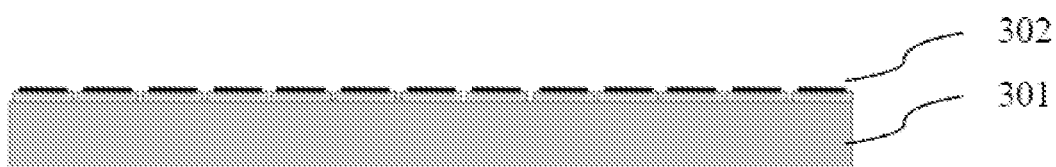


FIG. 6A

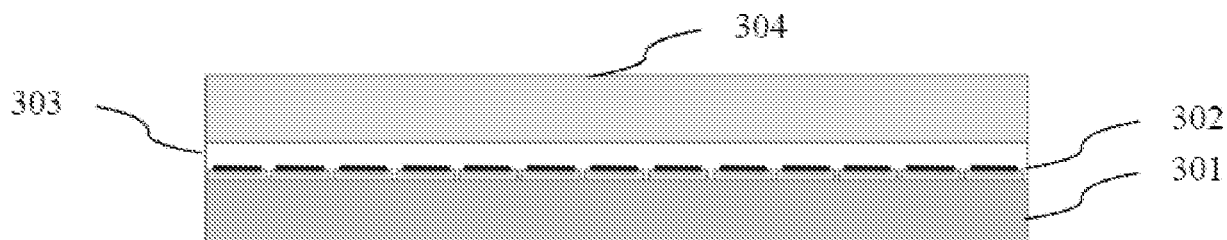


FIG. 6B

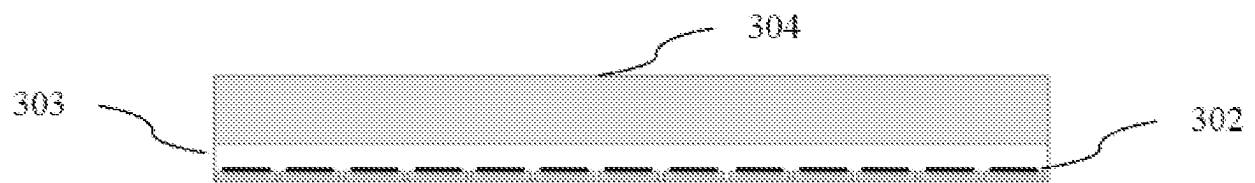


FIG. 6C

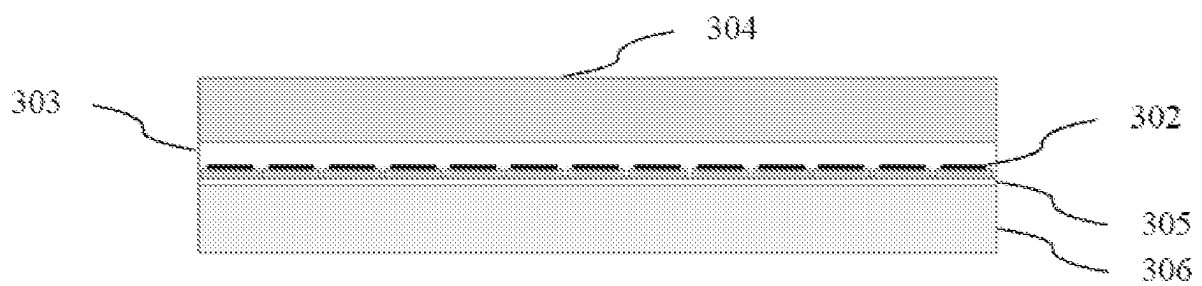


FIG. 6D

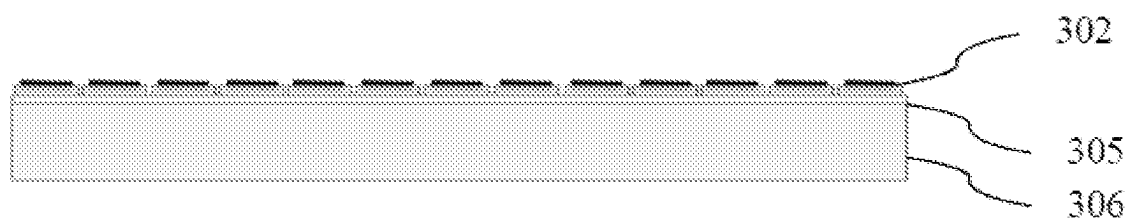


FIG. 6E

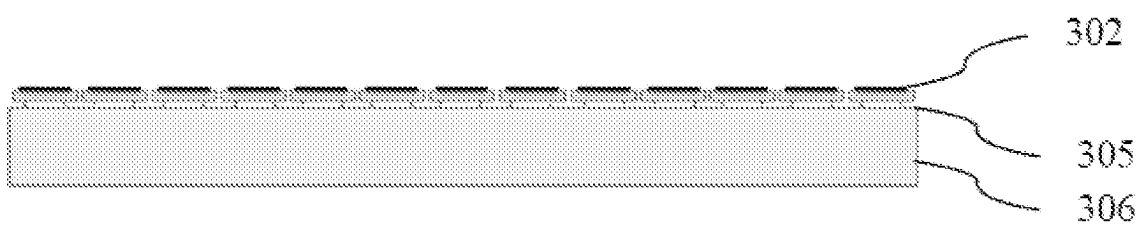


FIG. 6F

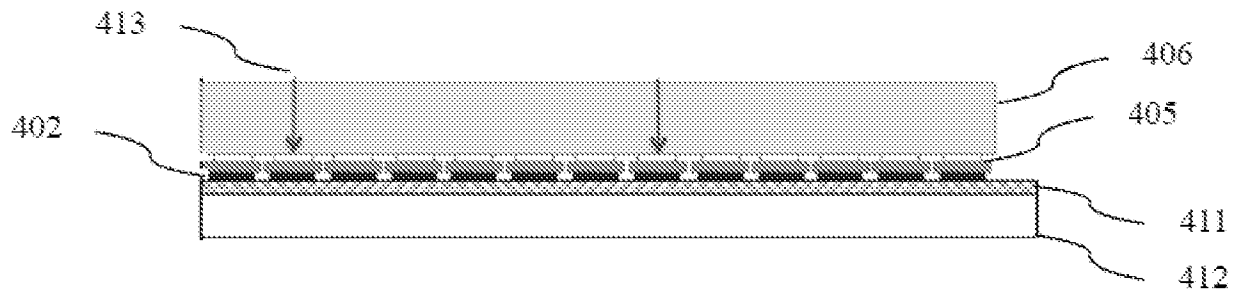


FIG. 7A

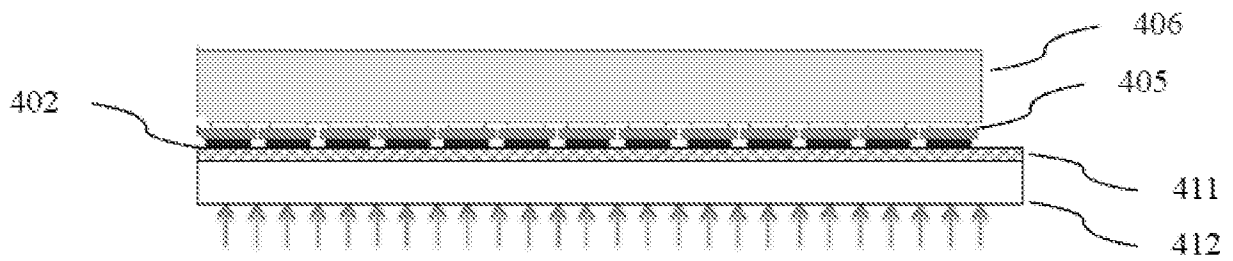


FIG. 7B

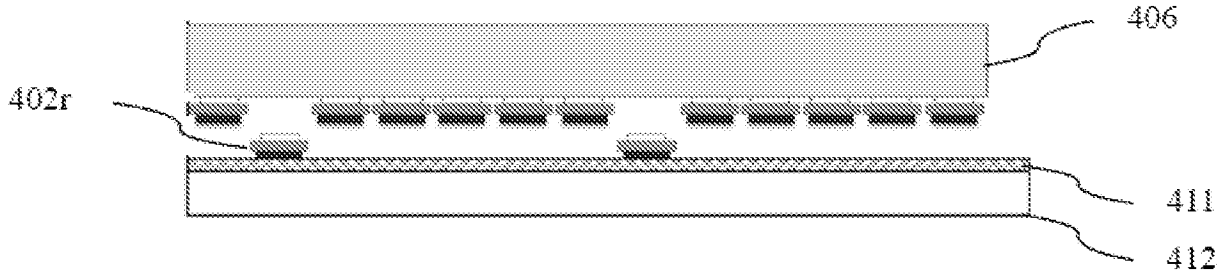


FIG. 7C

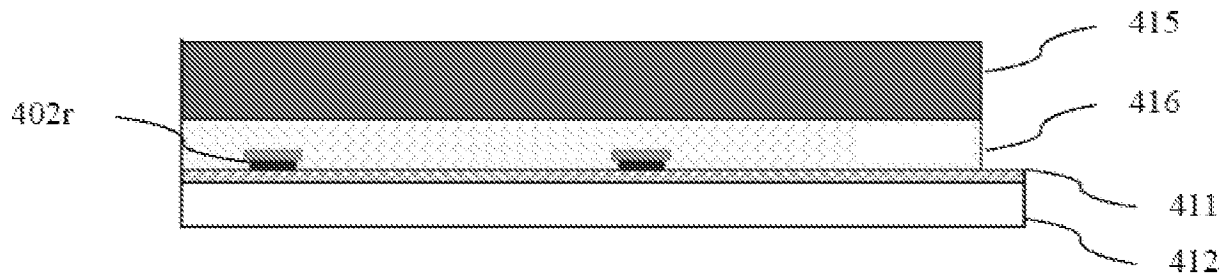


FIG. 7D

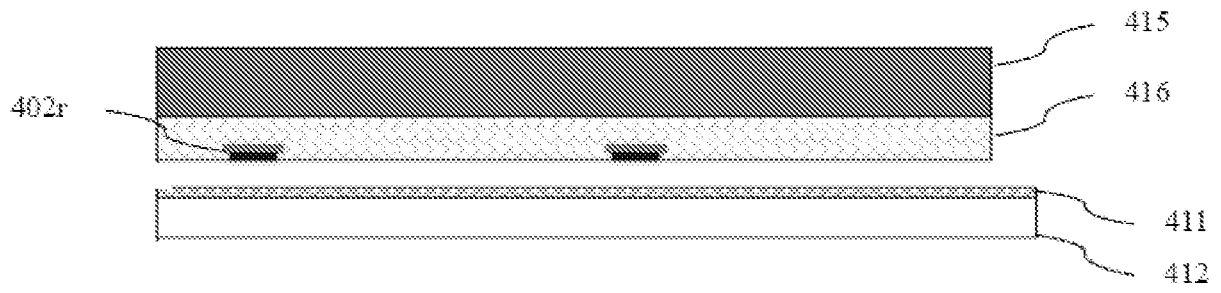


FIG. 7E

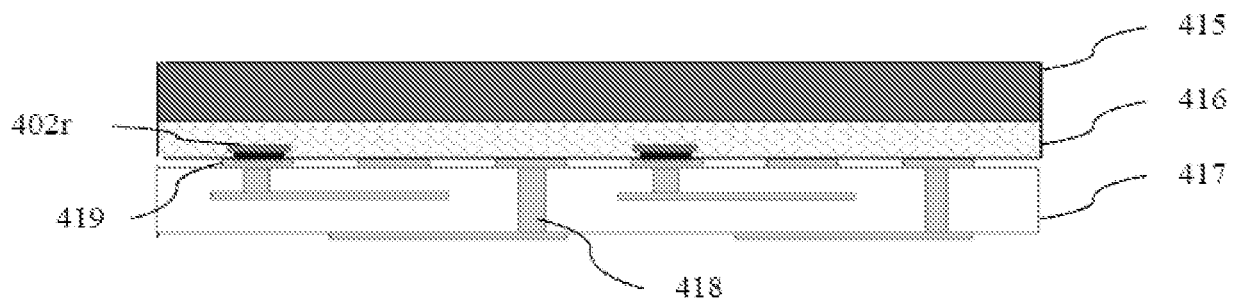


FIG. 7F

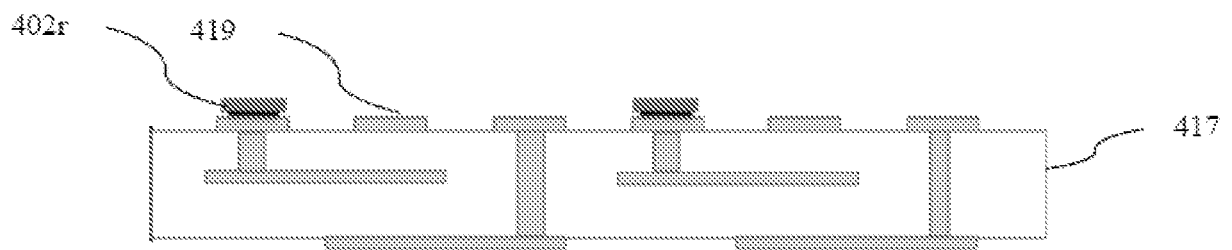


FIG. 7G

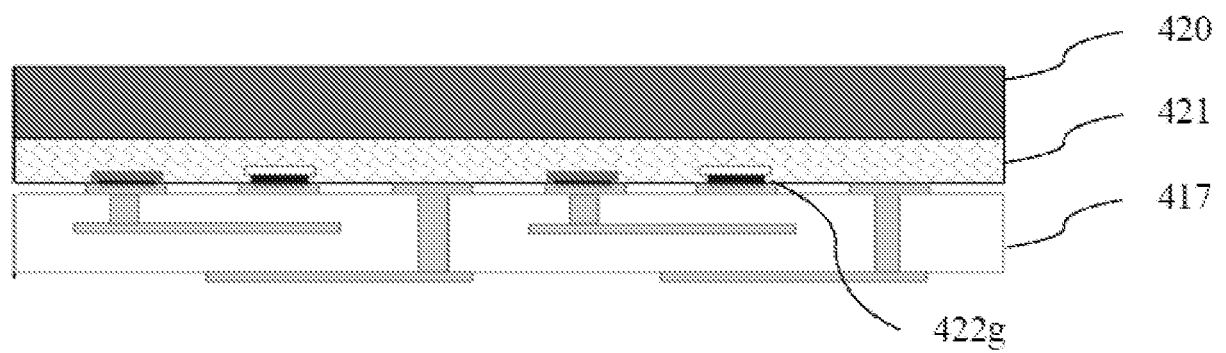


FIG. 7H

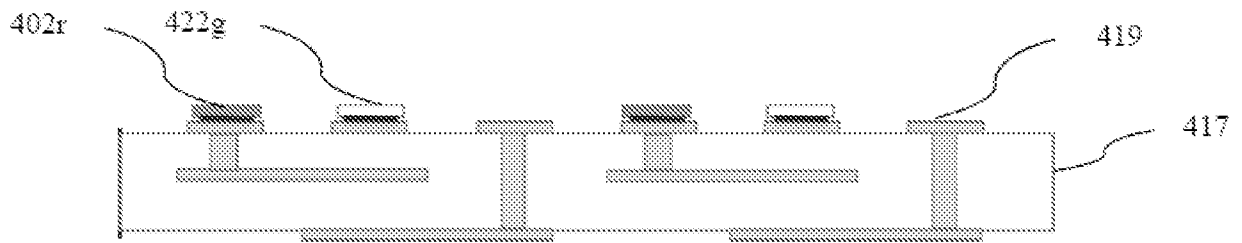


FIG. 7I

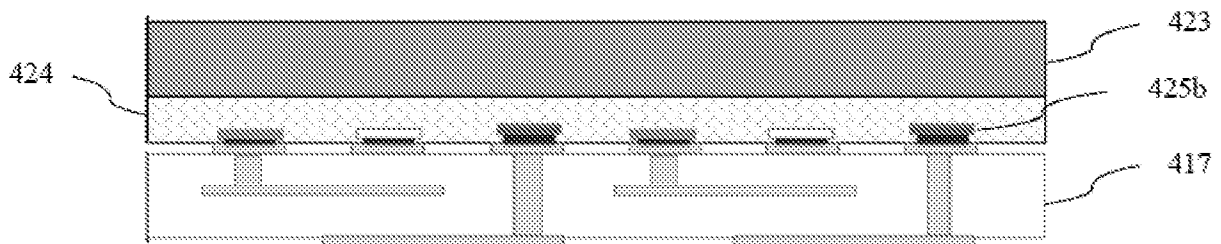


FIG. 7J

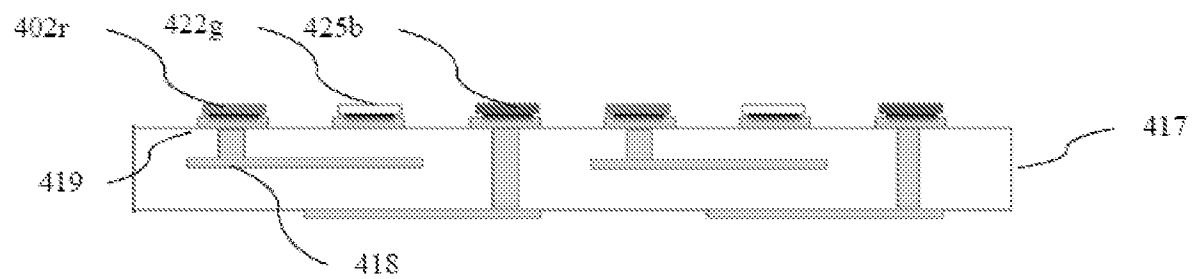


FIG. 7K

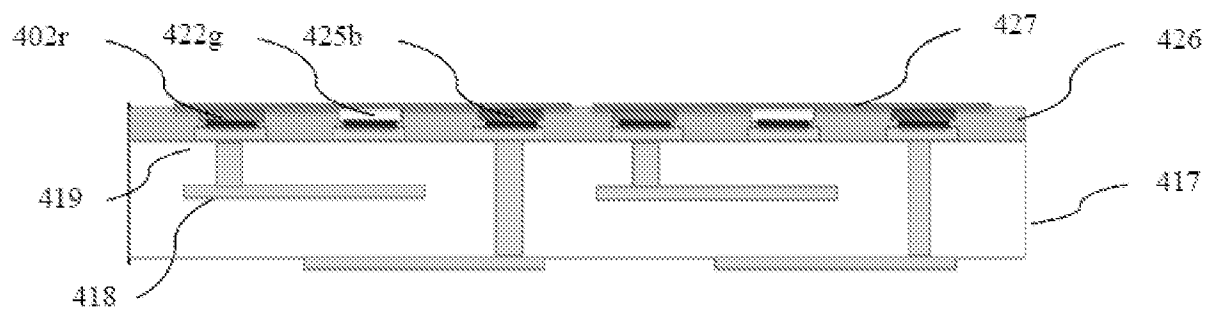


FIG. 7L

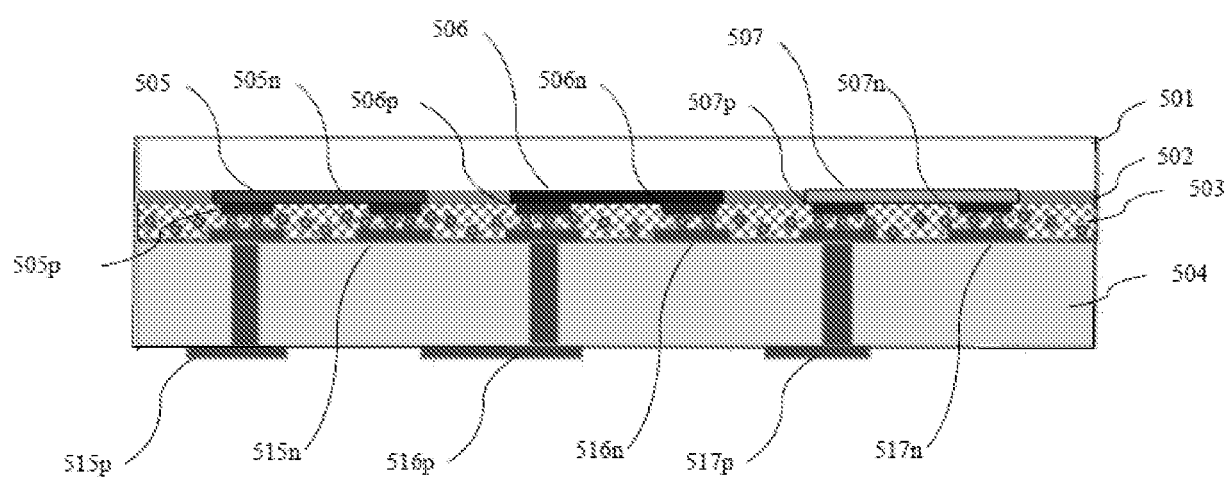


FIG. 8

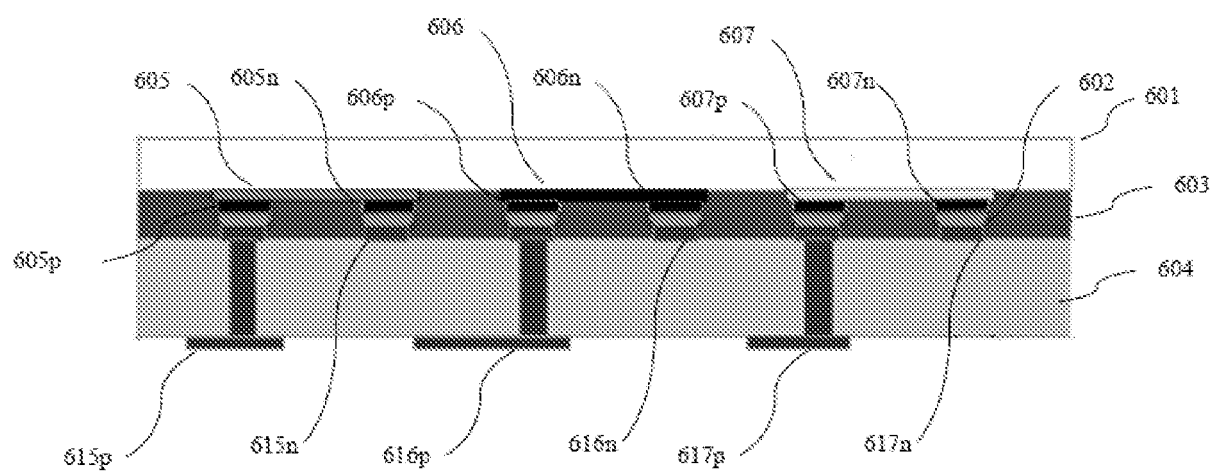


FIG. 9

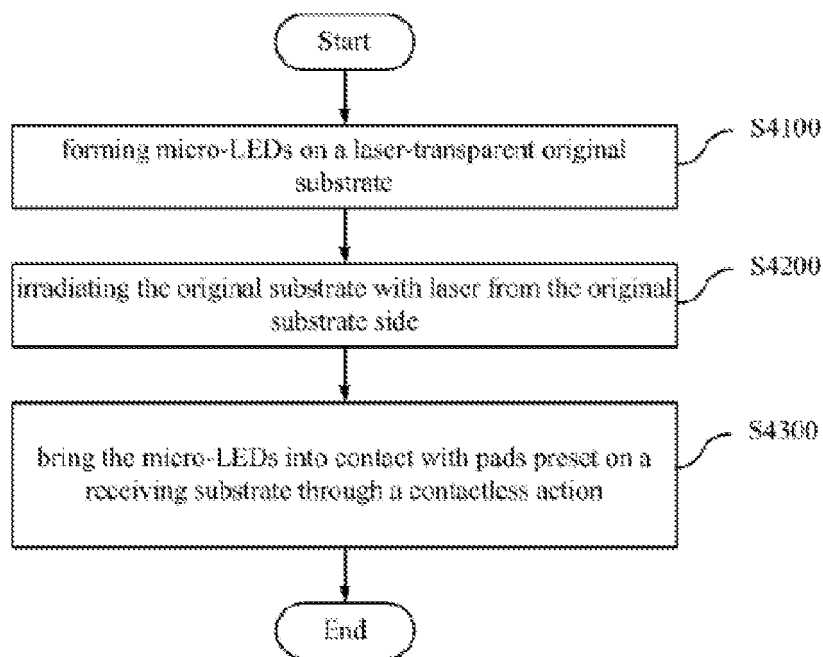


FIG. 10

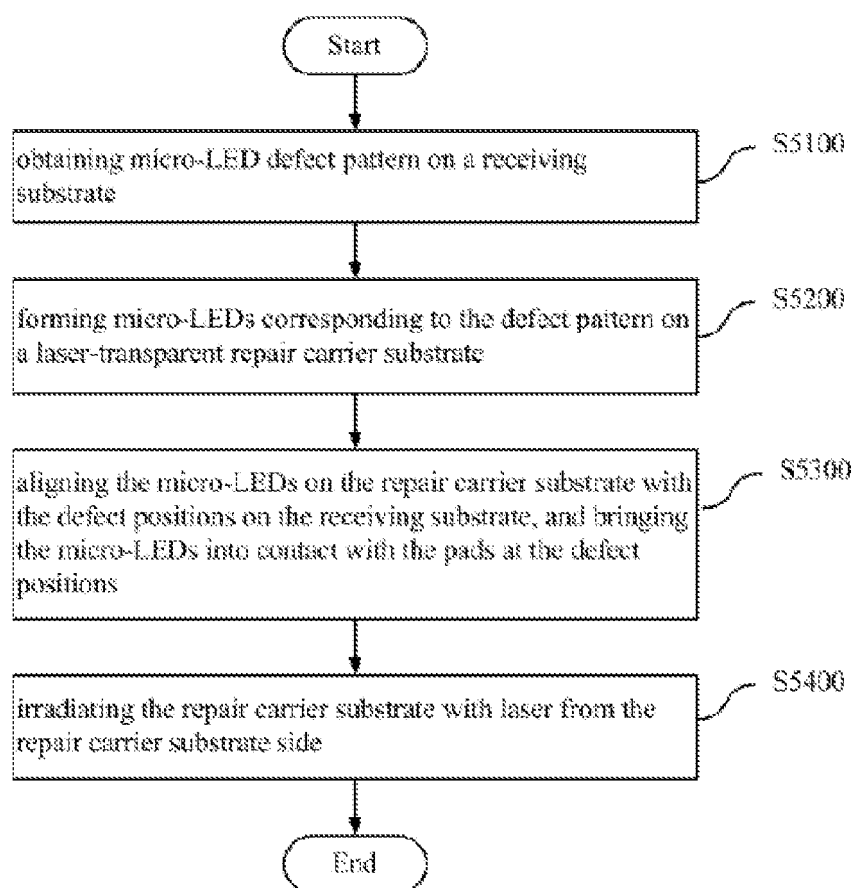


FIG. 11

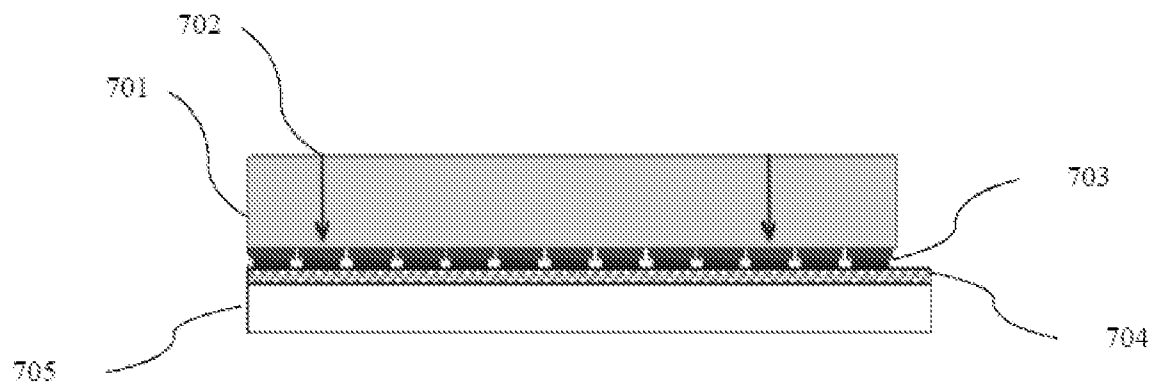


FIG. 12A

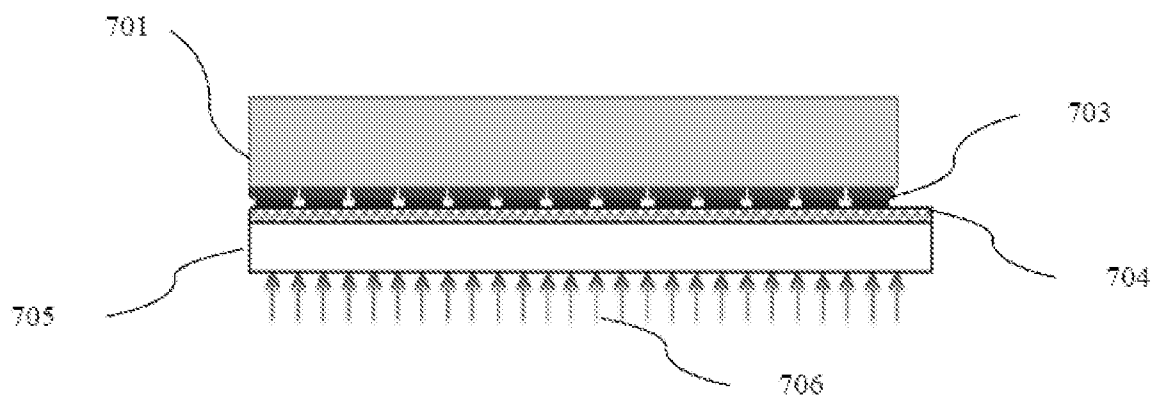


FIG. 12B

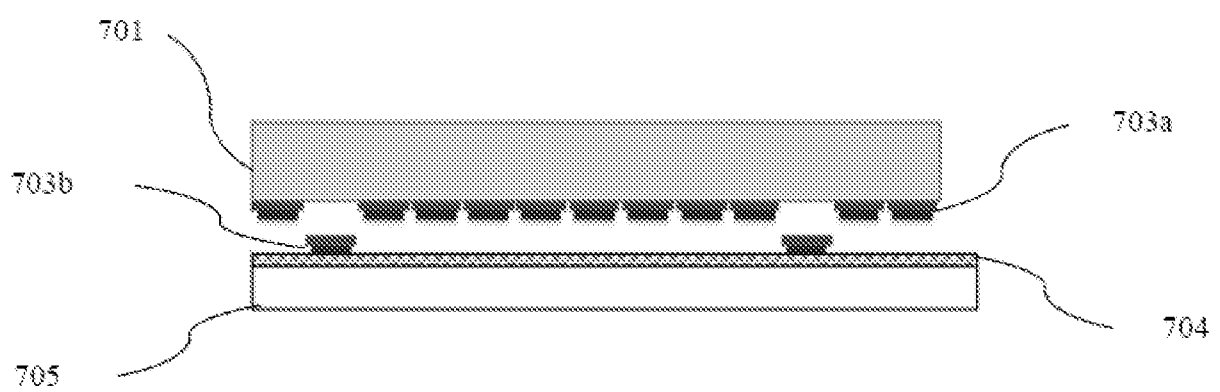


FIG. 12C

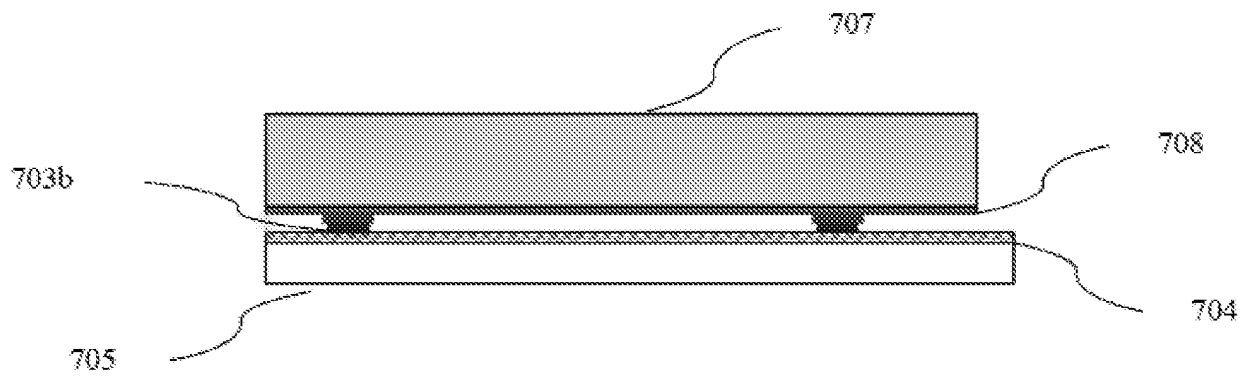


FIG. 12D

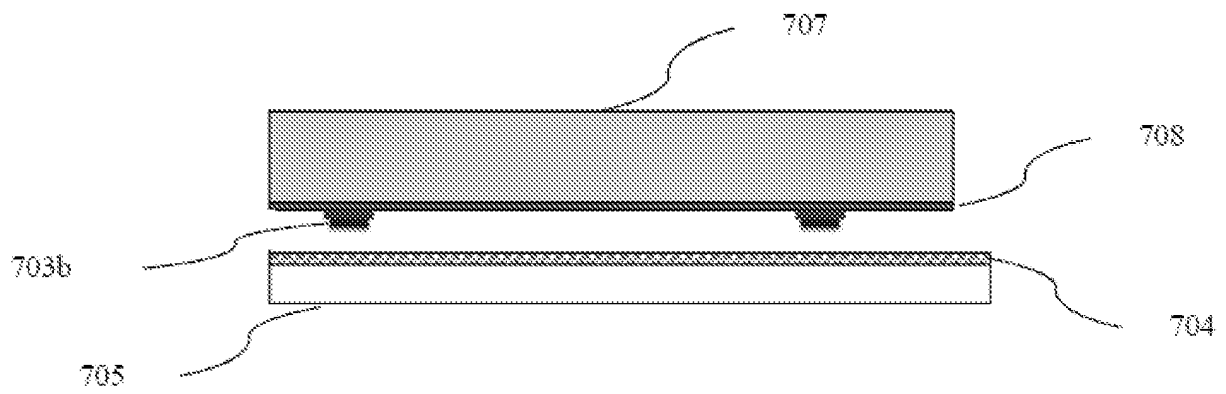


FIG. 12E

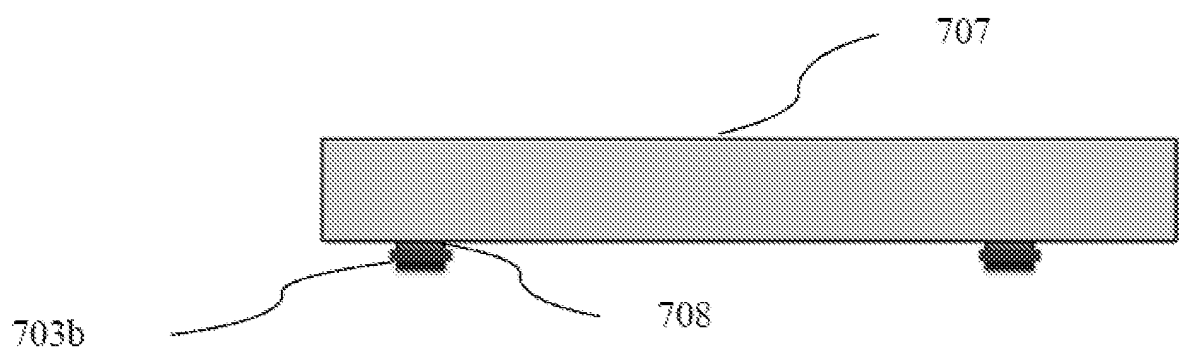


FIG. 12F

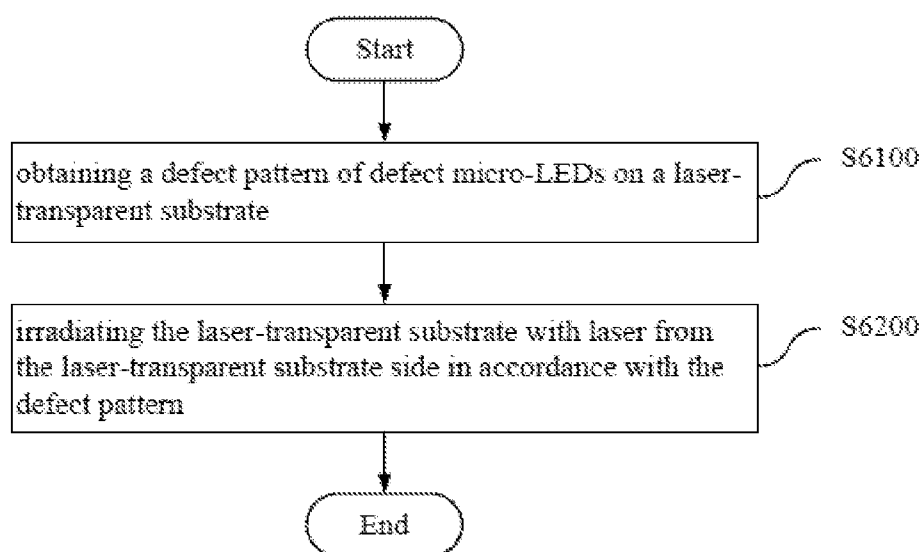


FIG. 13

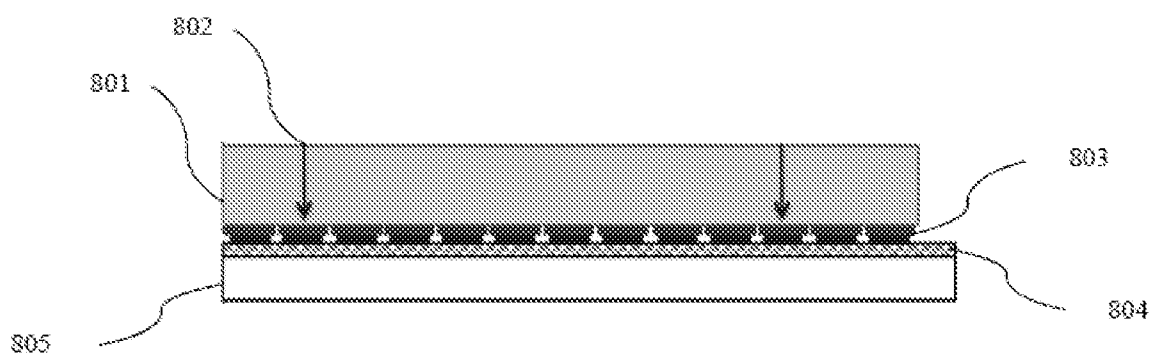


FIG. 14A

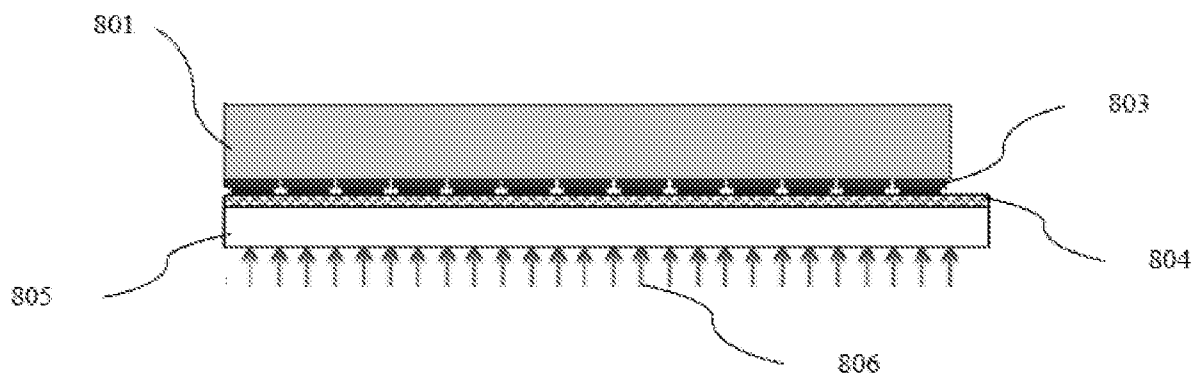


FIG. 14B

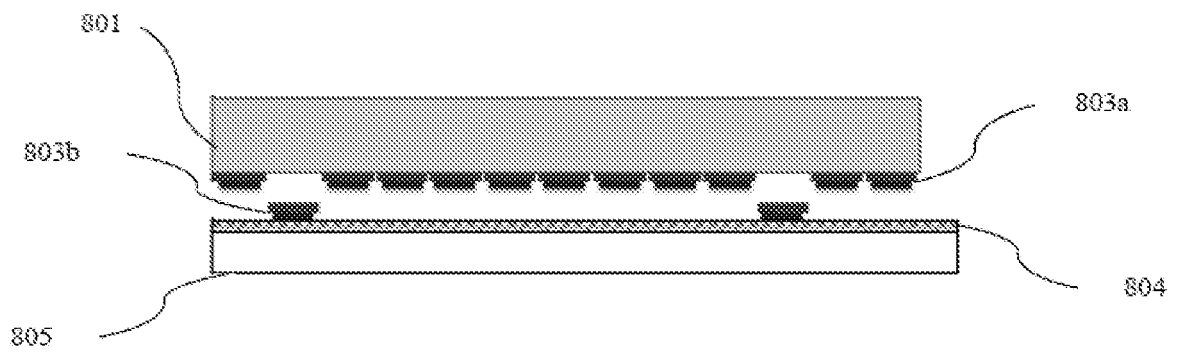


FIG. 14C

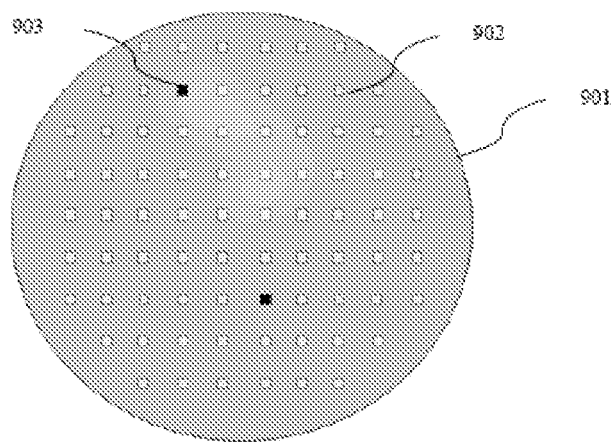


FIG. 15A

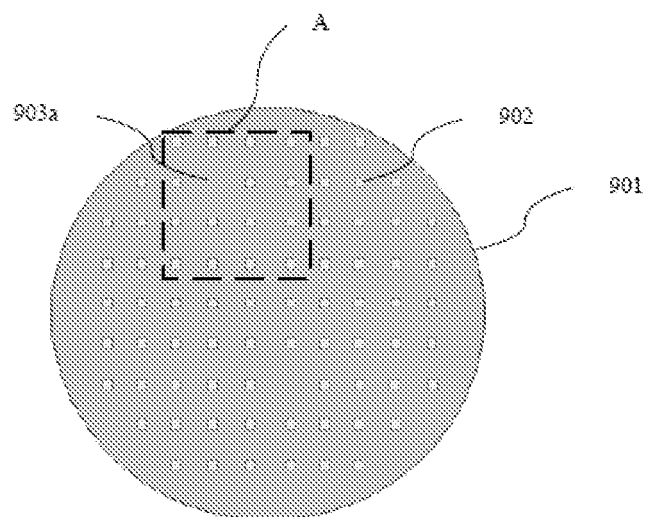


FIG. 15B

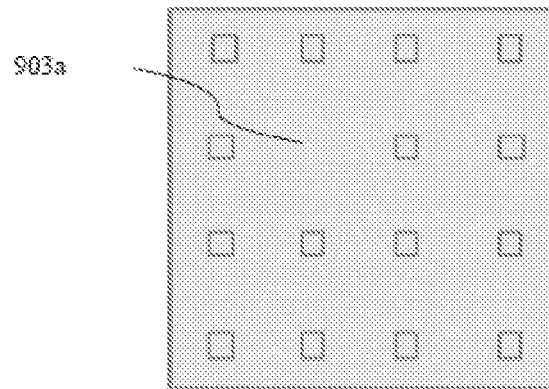


FIG. 16A

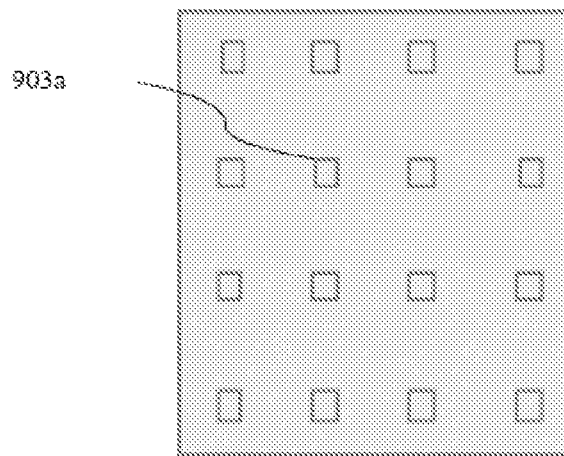


FIG. 16B

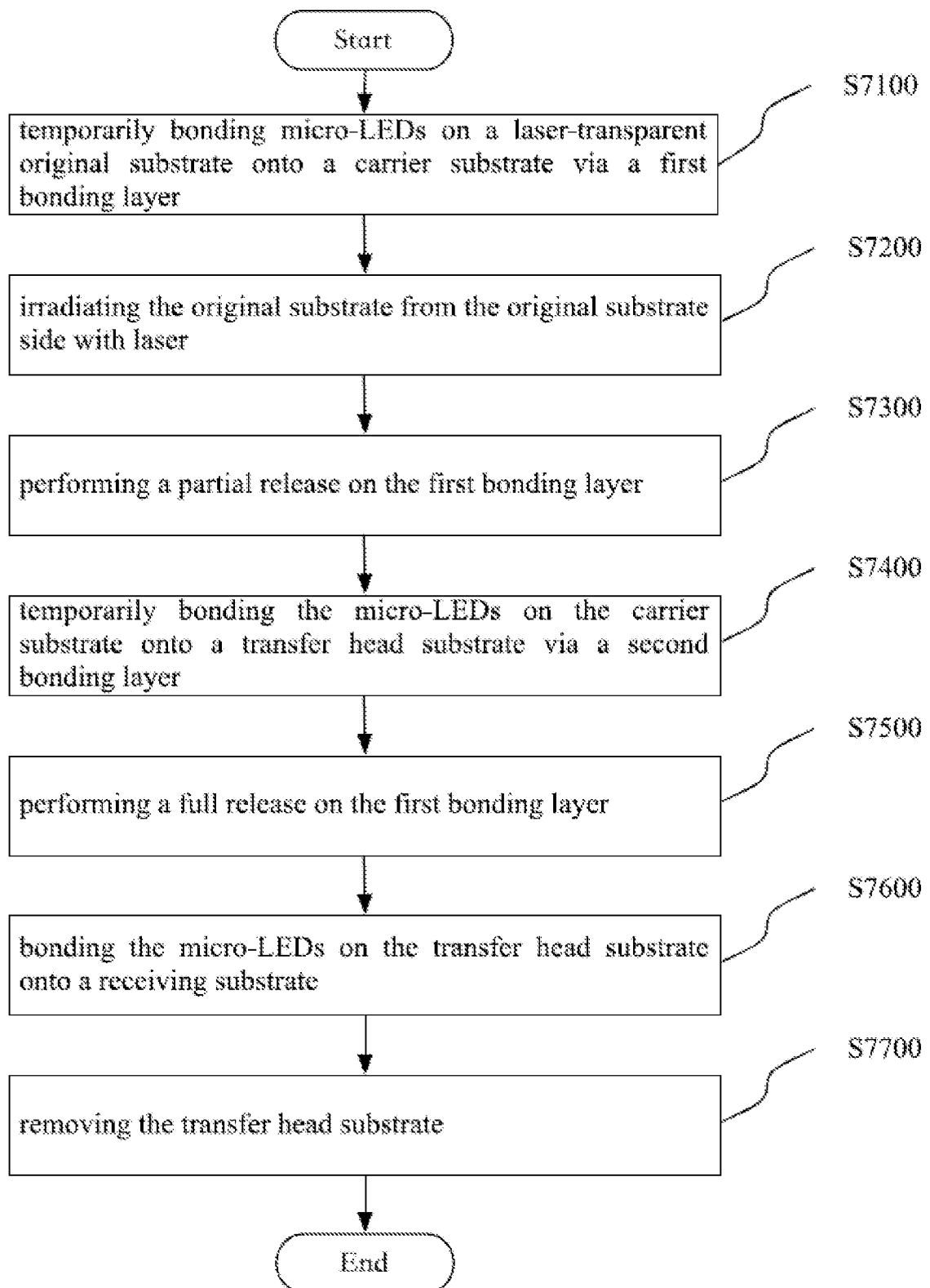


FIG. 17

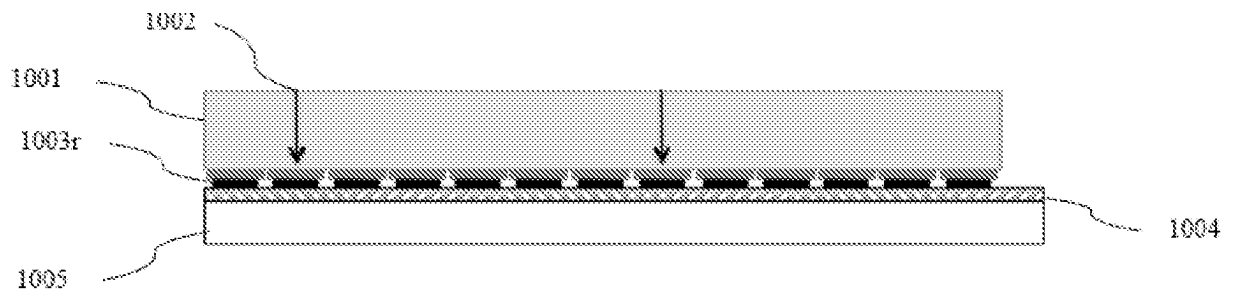


FIG. 18A

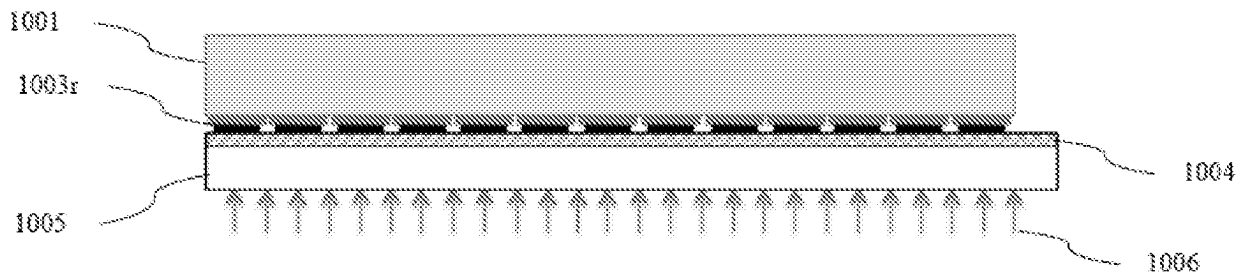


FIG. 18B

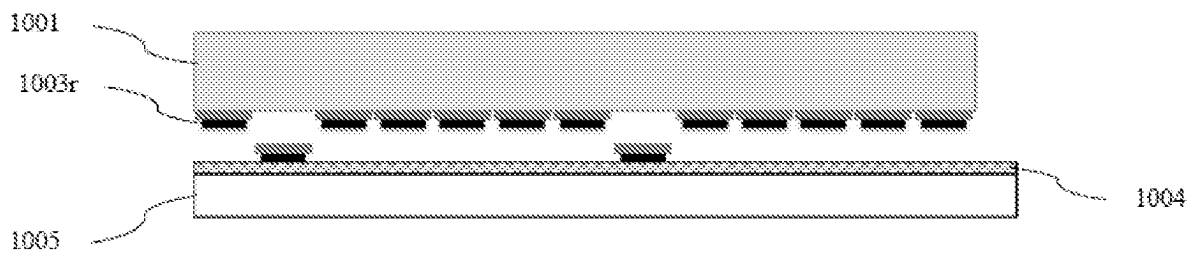


FIG. 18C

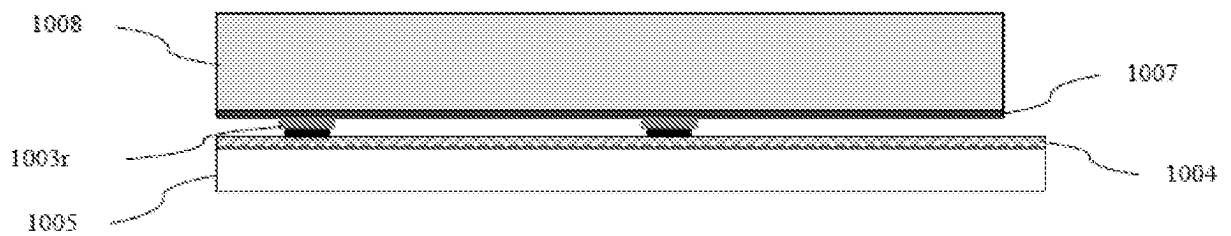


FIG. 18D

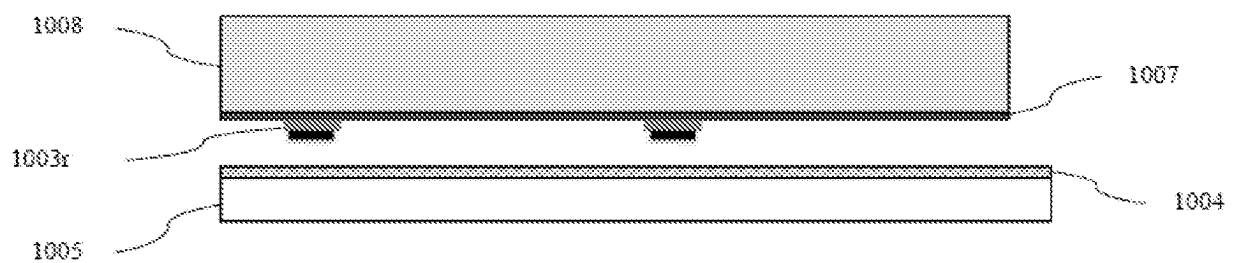


FIG. 18E

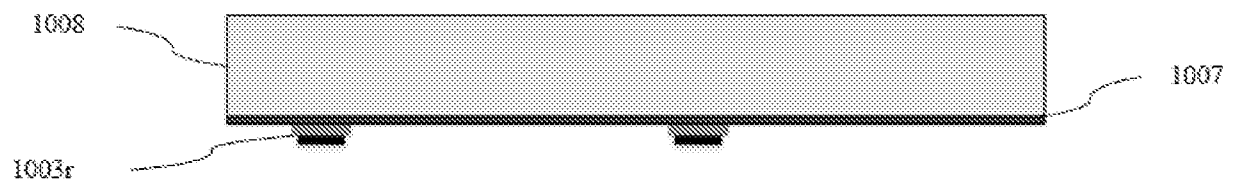


FIG. 18F

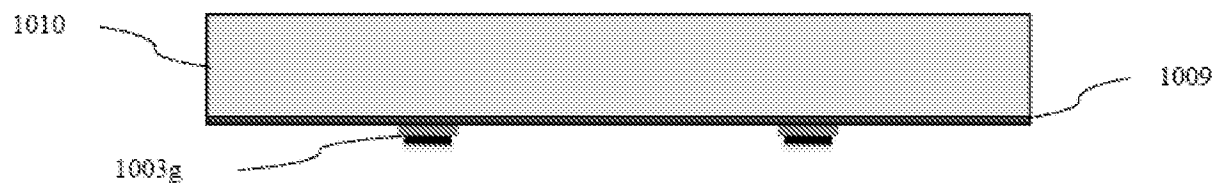


FIG. 18G

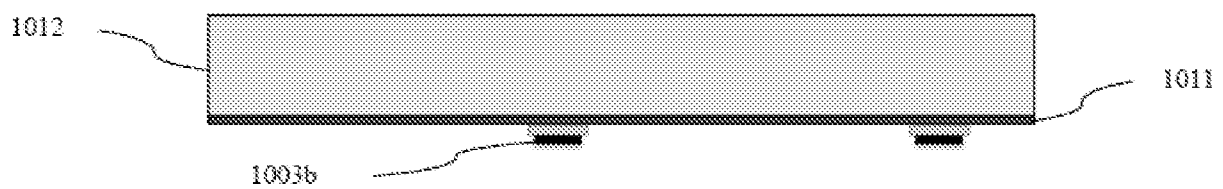


FIG. 18H

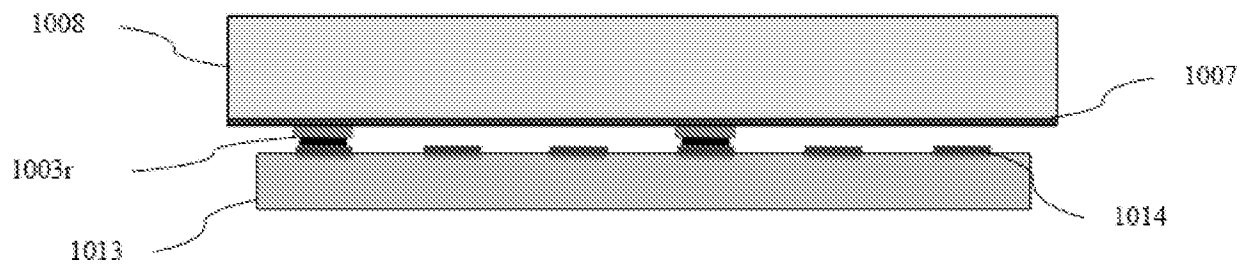


FIG. 18I

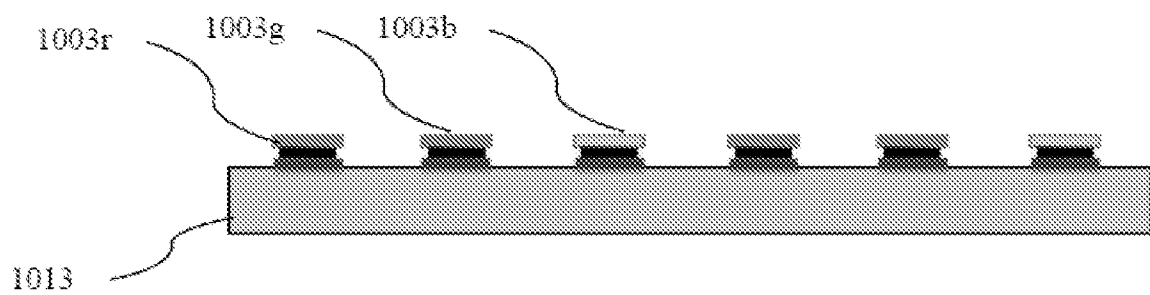


FIG. 18J

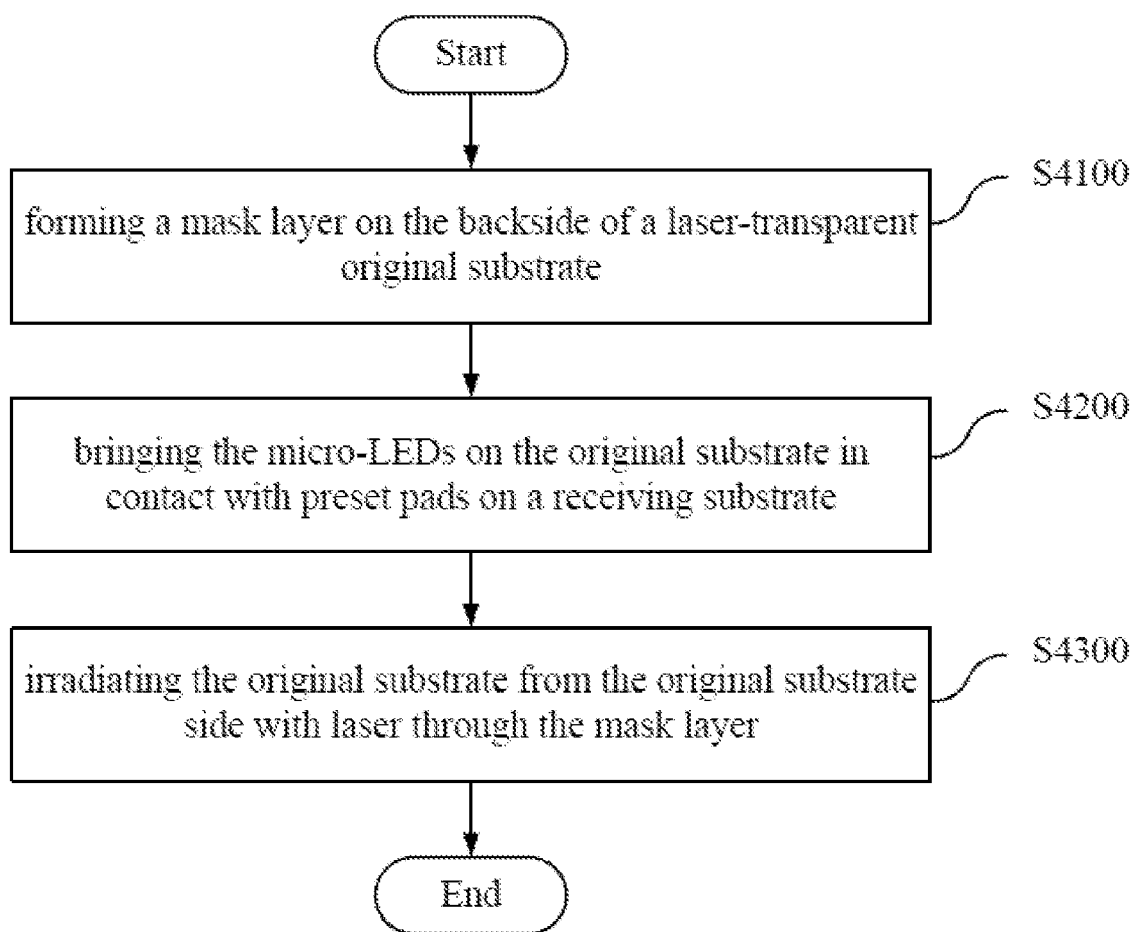


FIG. 19

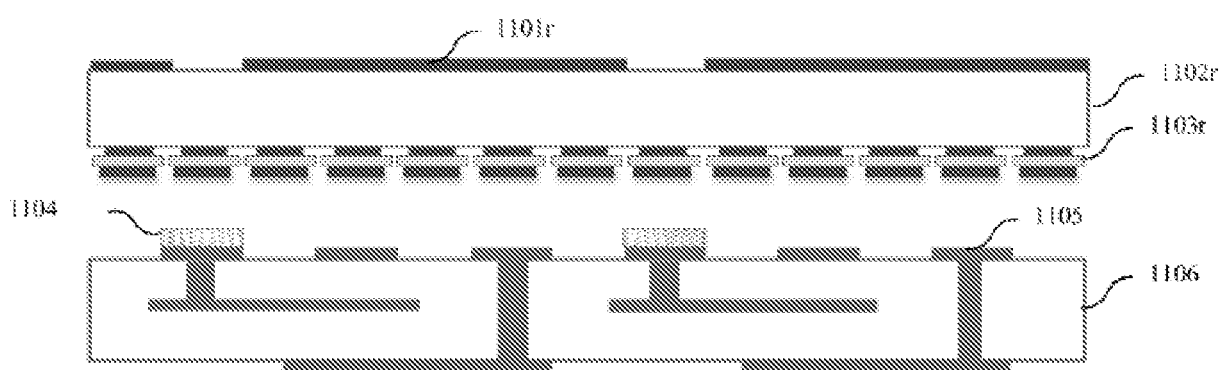


FIG. 20A

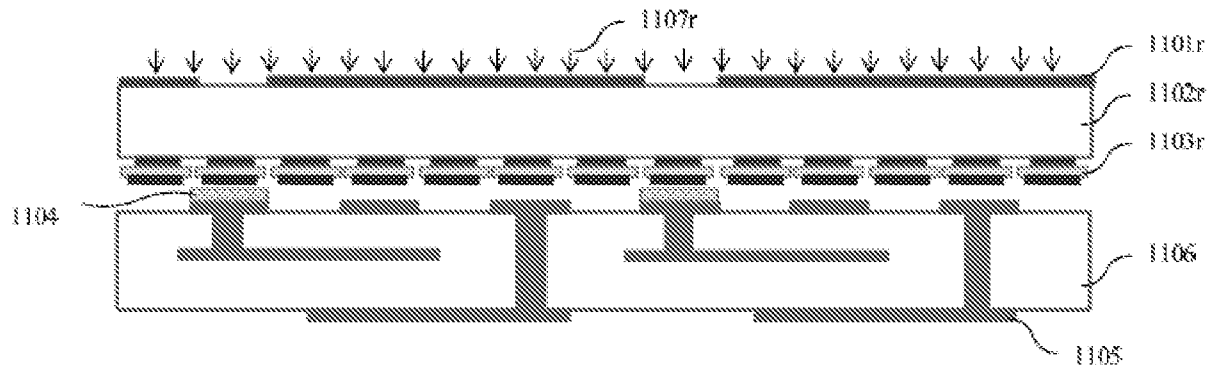


FIG. 20B

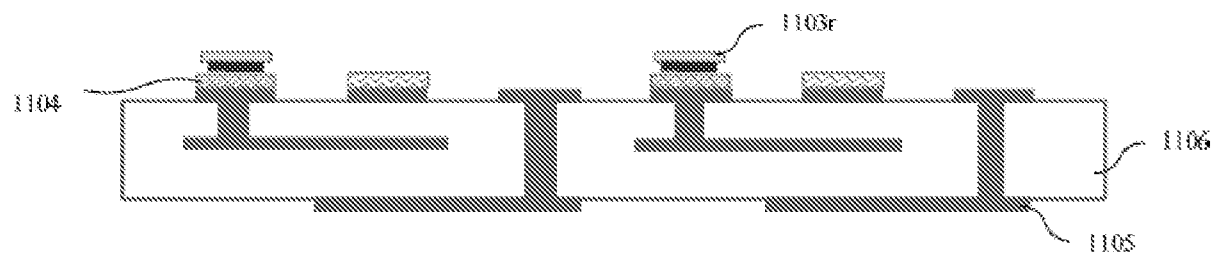


FIG. 20C

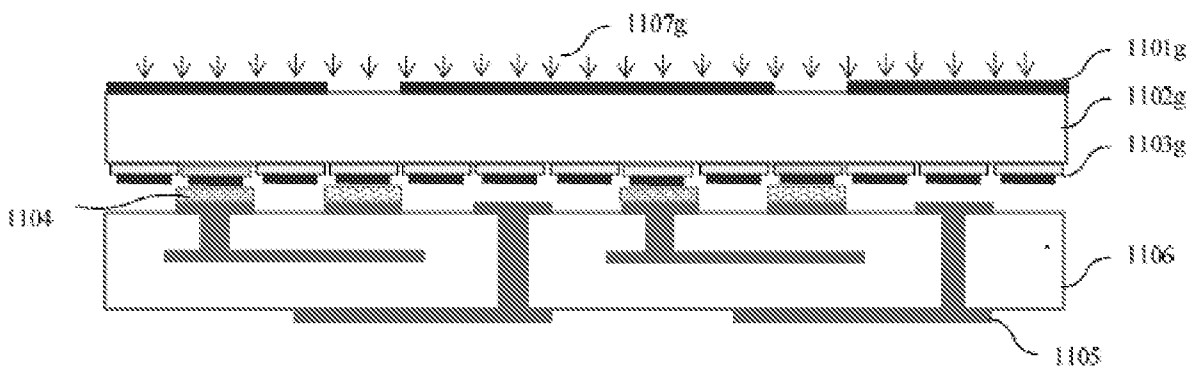


FIG. 20D

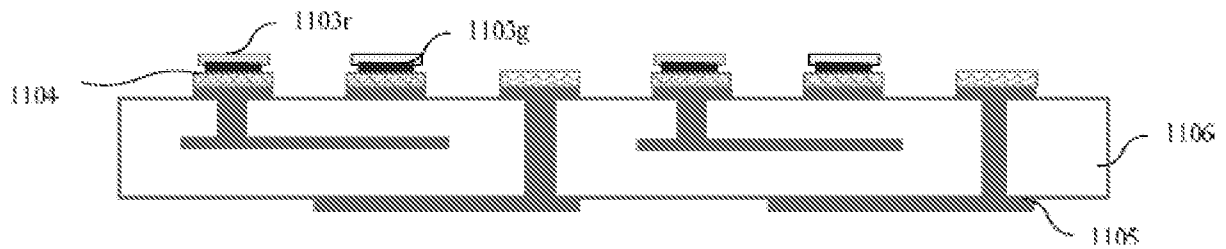


FIG. 20E

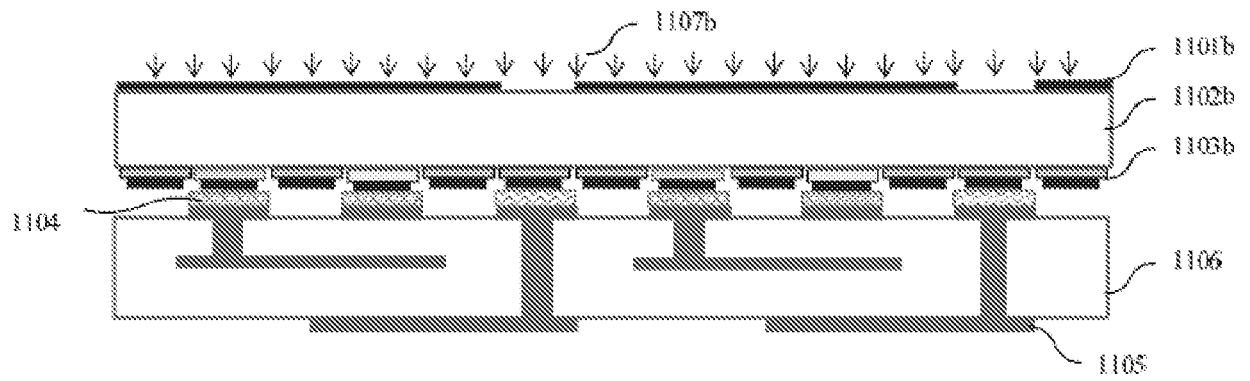


FIG. 20F

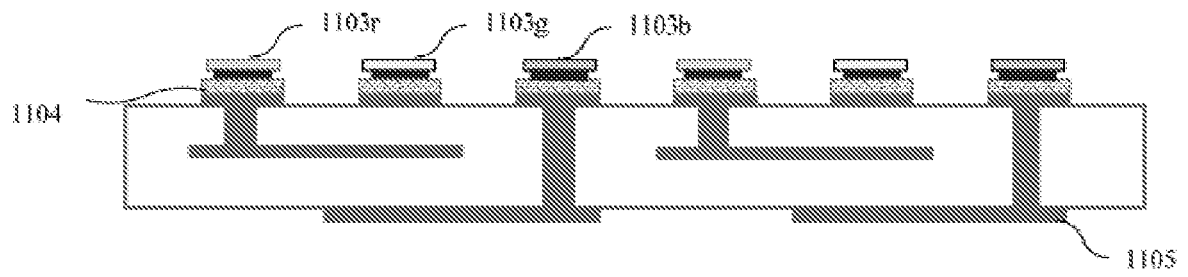


FIG. 20G

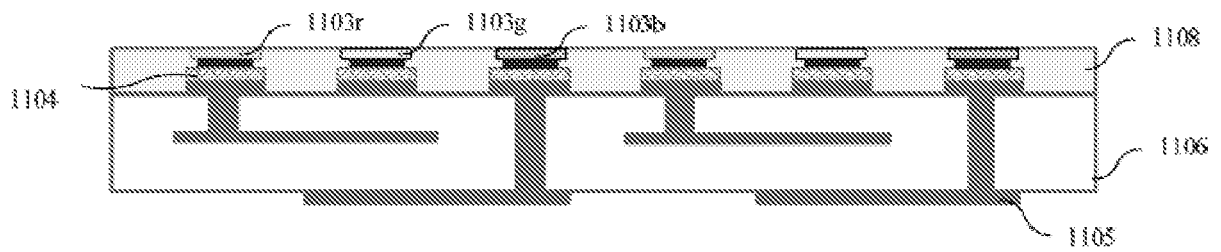


FIG. 20H

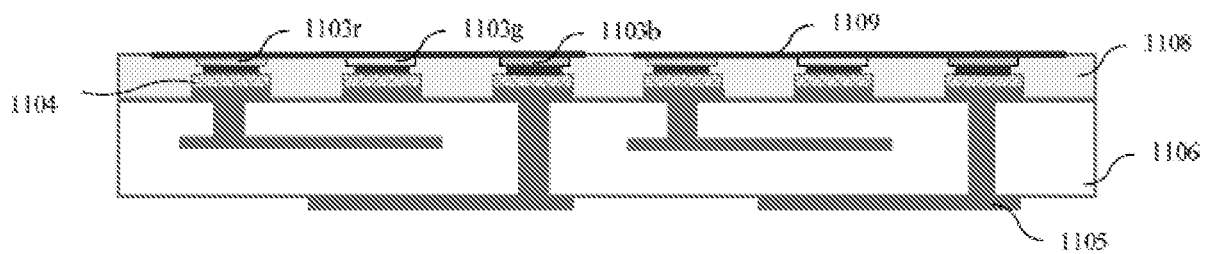


FIG. 20I

REFERENCES CITED IN THE DESCRIPTION

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- US 8426227 B1 [0006]
- US 20110151602 A1 [0007]
- US 20110133216 A1 [0008]
- WO 2015107290 A2 [0009]

专利名称(译)	微型LED器件的微型LED透射方法及其制造方法		
公开(公告)号	EP3248226B1	公开(公告)日	2020-02-26
申请号	EP2015907618	申请日	2015-11-04
[标]申请(专利权)人(译)	歌尔声学股份有限公司		
申请(专利权)人(译)	歌尔声学股份有限公司.		
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代理机构(译)	HÜBNER, 胃食管反流病		
其他公开文献	EP3248226A4 EP3248226A1		
外部链接	Espacenet		

摘要(译)

本发明公开了一种微型LED的转移方法，制造方法，装置和电子设备。转移微型LED的方法包括：在激光透明的原始基板的背面上形成掩模层，其中，在原始基板的正面上形成微型LED；以及使原始基板上的微型LED与接收基板上的预设焊盘接触；然后，通过掩模层，用激光从原始基板一侧照射原始基板，以从微型基板上剥离微型LED。

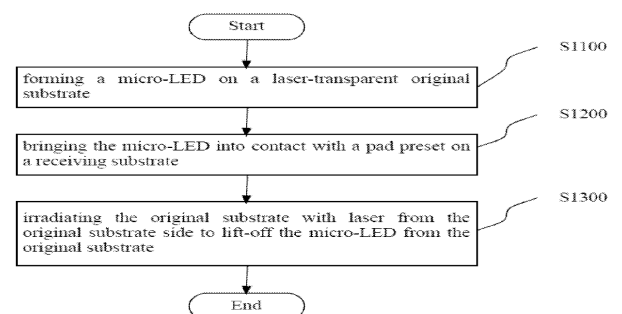


FIG. 1

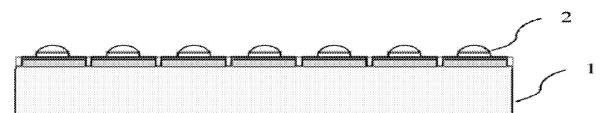


FIG. 2A